

SST26VF016B

2.5V/3.0V 16-Mbit Serial Quad I/OTM (SQITM) Flash Memory

Features

- · Single Voltage Read and Write Operations:
 - 2.7V-3.6V or 2.3V-3.6V
- · Serial Interface Architecture:
 - Nibble-wide multiplexed I/O's with SPI-like serial command structure
 - Mode 0 and Mode 3
 - x1/x2/x4 Serial Peripheral Interface (SPI) Protocol
- · High-Speed Clock Frequency:
 - 2.7V-3.6V: 104 MHz maximum
 - 2.3V-3.6V: 80 MHz maximum
- · Burst Modes:
 - Continuous linear burst
 - 8/16/32/64-byte linear burst with wrap-around
- · Superior Reliability:
 - Endurance: 100,000 Cycles (minimum)
 - Greater than 100 years data retention
- · Low-Power Consumption:
 - Active Read current: 15 mA (typical @ 104 MHz)
 - Standby current: 15 μA (typical)
- · Fast Erase Time:
 - Sector/Block Erase: 18 ms (typical), 25 ms (maximum)
 - Chip Erase: 35 ms (typical), 50 ms (maximum)
- · Page Program:
 - 256 bytes per page in x1 or x4 mode
- · End-of-Write Detection:
 - Software polling the BUSY bit in STATUS register
- · Flexible Erase Capability:
 - Uniform 4-Kbvte sectors
 - Four 8-Kbyte top and bottom parameter overlay blocks
 - One 32-Kbyte top and bottom overlay blocks
 - Uniform 64-Kbyte overlay blocks
- Write Suspend:
 - Suspend Program or Erase operation to access another block/sector
- Software Reset (RST) mode
- Software Write Protection:
 - Individual Block Write Protection with permanent lock-down capability
 - 64-Kbyte blocks, two 32-Kbyte blocks and eight 8-Kbyte parameter blocks

- Read Protection on top and bottom 8-Kbyte parameter blocks
- · Security ID:
 - One-Time-Programmable (OTP) 2-Kbyte, Secure ID
 - 64-bit unique, factory pre-programmed identifier
 - User-programmable area
- · Temperature Range:

Industrial: -40°C to +85°C
 Industrial Plus: -40°C to +105°C
 Extended: -40°C to +125°C

- Automotive AEC-Q100 Qualified
- · All devices are RoHS compliant

Packages

- 8-Lead SOIC (3.90 mm)
- 8-Lead SOIJ (5.28 mm)
- 8-Contact WDFN (6 mm x 5 mm)

Product Description

The Serial Quad I/O™ (SQI™) family of Flash memory devices features a six-wire, 4-bit I/O interface that allows for low-power, high-performance operation in a low pin-count package. SST26VF016B also supports full command-set compatibility to traditional Serial Peripheral Interface (SPI) protocol. System designs using SQI Flash devices occupy less board space and ultimately lower system costs.

All members of the 26 Series SQI family are manufactured with proprietary, high-performance CMOS SuperFlash® technology. The split-gate cell design and thick-oxide tunneling injector attain better reliability and manufacturability compared with alternate approaches.

SST26VF016B significantly improves performance and reliability, while lowering power consumption. These devices write (Program or Erase) with a single power supply of 2.3V-3.6V. The total energy consumed is a function of the applied voltage, current and time of application. Since for any given voltage range, the SuperFlash technology uses less current to program and has a shorter erase time, the total energy consumed during any Erase or Program operation is less than alternative Flash memory technologies.

See Figure 2-1 for pin assignments.

TO OUR VALUED CUSTOMERS

It is our intention to provide our valued customers with the best documentation possible to ensure successful use of your Microchip products. To this end, we will continue to improve our publications to better suit your needs. Our publications will be refined and enhanced as new volumes and updates are introduced.

If you have any questions or comments regarding this publication, please contact the Marketing Communications Department via E-mail at docerrors@microchip.com. We welcome your feedback.

Most Current Data Sheet

To obtain the most up-to-date version of this data sheet, please register at our Worldwide Web site at:

http://www.microchip.com

You can determine the version of a data sheet by examining its literature number found on the bottom outside corner of any page. The last character of the literature number is the version number, (e.g., DS30000000A is version A of document DS30000000).

Errata

An errata sheet, describing minor operational differences from the data sheet and recommended workarounds, may exist for current devices. As device/documentation issues become known to us, we will publish an errata sheet. The errata will specify the revision of silicon and revision of document to which it applies.

To determine if an errata sheet exists for a particular device, please check with one of the following:

- · Microchip's Worldwide Web site; http://www.microchip.com
- · Your local Microchip sales office (see last page)

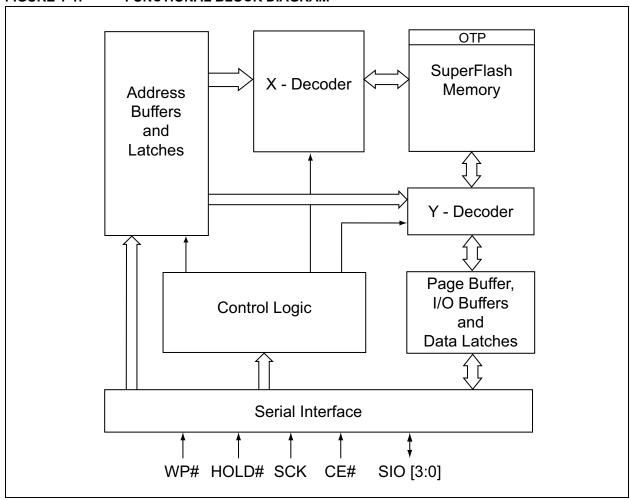
When contacting a sales office, please specify which device, revision of silicon and data sheet (include literature number) you are using.

Customer Notification System

Register on our web site at www.microchip.com to receive the most current information on all of our products.

1.0 BLOCK DIAGRAM

FIGURE 1-1: FUNCTIONAL BLOCK DIAGRAM



2.0 PIN DESCRIPTION

FIGURE 2-1: PIN DESCRIPTIONS

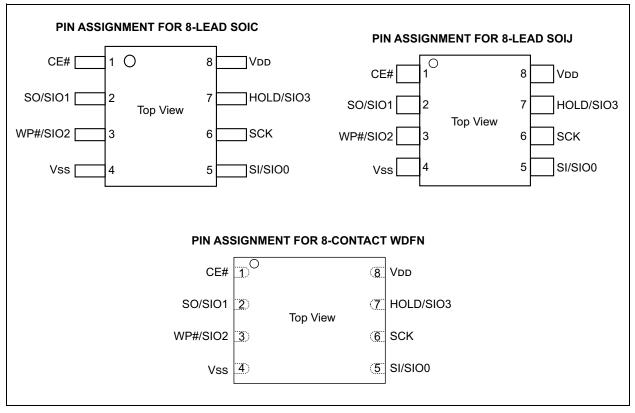


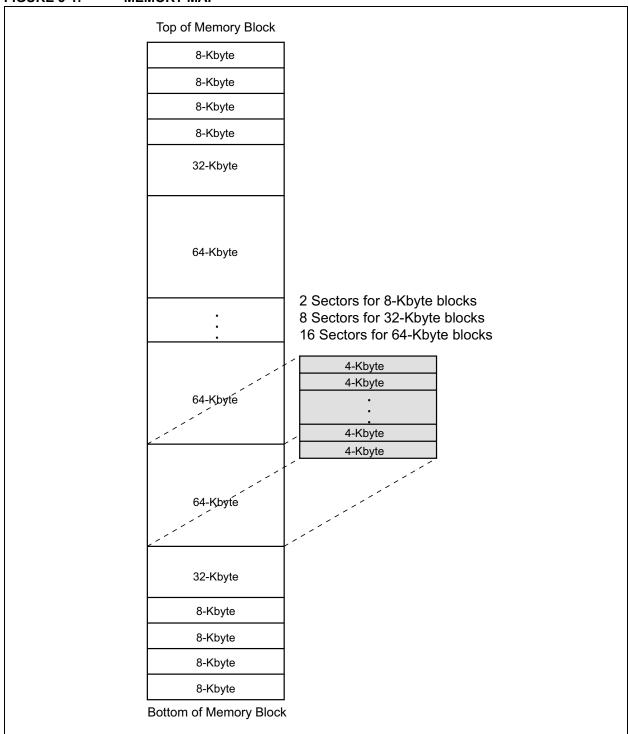
TABLE 2-1: PIN DESCRIPTION

Symbol	Pin Name	Functions
CE#	Chip Enable	The device is enabled by a high-to-low transition on CE#. CE# must remain low for the duration of any command sequence; or in the case of Write operations, for the command/data input sequence.
so	Serial Data Output for SPI mode	Transfer data serially out of the device. Data is shifted out on the falling edge of the serial clock. SO is the default state after a Power-on Reset.
SIO[3:0]	Serial Data Input/Output	Transfer commands, addresses or data serially into the device or data out of the device. Inputs are latched on the rising edge of the serial clock. Data are shifted out on the falling edge of the serial clock. The Enable Quad I/O (EQIO) command instruction configures these pins for Quad I/O mode.
WP#	Write-Protect	The WP# is used in conjunction with the WPEN and IOC bits in the Configuration register to prohibit write operations to the Block Protection register. This pin only works in SPI, single-bit and dual-bit Read mode.
Vss	Ground	
SI	Serial Data Input for SPI mode	Transfer commands, addresses or data serially into the device. Inputs are latched on the rising edge of the serial clock. SI is the default state after a Power-on Reset.
SCK	Serial Clock	Provide the timing of the serial interface. Commands, addresses or input data are latched on the rising edge of the clock input, while output data are shifted out on the falling edge of the clock input.
HOLD#	Hold	Temporarily stops serial communication with the SPI Flash memory while the device is selected. This pin only works in SPI, single-bit and dual-bit Read mode and must be tied high when not in use.
VDD	Power Supply	Provide power supply voltage.

3.0 MEMORY ORGANIZATION

The SST26VF016B SQI memory array is organized in uniform, 4-Kbyte erasable sectors with the following erasable blocks: eight 8-Kbyte parameter, two 32-Kbyte overlay and thirty 64-Kbyte overlay blocks (see Figure 3-1).

FIGURE 3-1: MEMORY MAP



4.0 DEVICE OPERATION

SST26VF016B supports both Serial Peripheral Interface (SPI) bus protocol and a 4-bit multiplexed SQI bus protocol. To provide backward compatibility to traditional SPI Serial Flash devices, the device's initial state after a Power-on Reset is SPI mode which supports multi-I/O (x1/x2/x4) Read/Write commands. A command instruction configures the device to SQI mode. The dataflow in the SQI mode is similar to the SPI mode, except it uses four multiplexed I/O signals for command, address and data sequence.

SQI Flash Memory supports both Mode 0 (0,0) and Mode 3 (1,1) bus operations. The difference between the two modes is the state of the SCK signal when the bus host is in standby mode and no data are being transferred.

The SCK signal is low for Mode 0 and SCK signal is high for Mode 3. For both modes, the Serial Data I/O (SIO[3:0]) is sampled at the rising edge of the SCK clock signal for input and driven after the falling edge of the SCK clock signal for output. The traditional SPI protocol uses separate input (SI) and output (SO) data signals as shown in Figure 4-1. The SQI protocol uses four multiplexed signals, SIO[3:0], for both data in and data out, as shown in Figure 4-2. This means the SQI protocol quadruples the traditional bus transfer speed at the same clock frequency, without the need for more pins on the package.

FIGURE 4-1: SPI PROTOCOL (TRADITIONAL 25 SERIES SPI DEVICE)

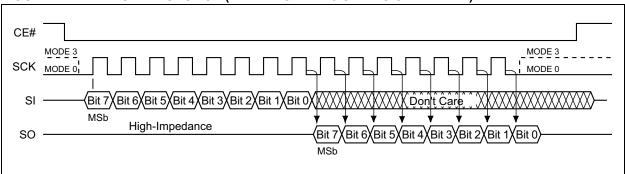
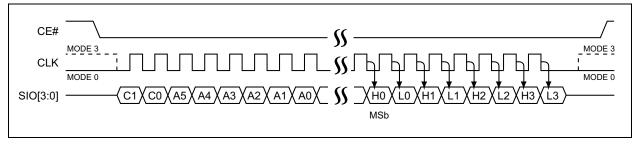


FIGURE 4-2: SQI SERIAL QUAD I/O PROTOCOL



4.1 Device Protection

SST26VF016B offers a flexible memory protection scheme that allows the protection state of each individual block to be controlled separately. In addition, the Write Protection Lock-Down register prevents any change of the lock status during device operation. To avoid inadvertent writes during power-up, the device is write-protected by default after a Power-on Reset cycle. A Global Block Protection Unlock command offers a single command cycle that unlocks the entire memory array for faster manufacturing throughput.

For extra protection, there is an additional nonvolatile register that can permanently write-protect the Block Protection register bits for each individual block.

Each of the corresponding lock-down bits are One-Time-Programmable (OTP) — once written, they cannot be erased. Data that had been previously programmed into these blocks cannot be altered by programming or erase and are not reversible.

4.1.1 INDIVIDUAL BLOCK PROTECTION

SST26VF016B has a Block Protection register which provides a software mechanism to write-lock the individual memory blocks and write-lock and/or read-lock the individual parameter blocks. The Block Protection register is 48-bit wide: two bits each for the eight 8-Kbyte parameter blocks (write-lock and read-lock), and one bit each for the remaining 32-Kbyte and 64-Kbyte overlay blocks (write-lock). See Table 5-6 for address range protected per register bit.

Each bit in the Block Protection register (BPR) can be written to a '1' (protected) or '0' (unprotected). For the parameter blocks, the Most Significant bit is for read-lock and the Least Significant bit is for write-lock. Read-locking the parameter blocks provides additional security for sensitive data after retrieval (e.g., after initial boot). If a block is read-locked, all reads to the block return data 00H.

The Write Block Protection Register command is a two-cycle command which requires that Write Enable (WREN) is executed prior to the Write Block Protection Register command. The Global Block Protection Unlock command clears all write protection bits in the Block Protection register.

4.1.2 WRITE PROTECTION LOCK-DOWN (VOLATILE)

To prevent changes to the Block Protection register, use the Lock-Down Block Protection Register (LBPR) command to enable Write Protection Lock-Down. Once Write Protection Lock-Down is enabled, the Block Protection register cannot be changed. To avoid inadvertent lock-down, the WREN command must be executed prior to the LBPR command.

To reset Write Protection Lock-Down, performing a power cycle on the device is required. The Write Protection Lock-Down status may be read from the STATUS register.

4.1.3 WRITE-LOCK LOCK-DOWN (NONVOLATILE)

The nonvolatile Write-Lock Lock-Down register is an alternate register that permanently prevents changes to the block-protect bits. The nonvolatile Write-Lock Lock-Down register (nVWLDR) is 40-bit wide per device: one bit each for the eight 8-Kbyte parameter blocks and one bit each for the remaining 32-Kbyte and 64-Kbyte overlay blocks. See Table 5-6 for address range protected per register bit.

Writing '1' to any or all of the nVWLDR bits disables the change mechanism for the corresponding Write-Lock bit in the BPR and permanently sets this bit to a '1' (protected) state. After this change, both bits will be set to '1', regardless of the data entered in subsequent writes to either the nVWLDR or the BPR.

Subsequent writes to the nVWLDR can only alter available locations that have not been previously written to a '1'. This method provides write protection for the corresponding memory-array block by protecting it from future program or erase operations.

Writing a '0' in any location in the nVWLDR has no effect on either the nVWLDR or the corresponding Write-Lock bit in the BPR.

Note that if the Block Protection register had been previously locked down (see Section 4.1.2 "Write Protection Lock-Down (Volatile)"), the device must be power cycled before using the nVWLDR. If the Block Protection register is locked down and the Write nVWLDR command is accessed, the command will be ignored.

4.2 Hardware Write Protection

The hardware Write Protection pin (WP#) is used in conjunction with the WPEN and IOC bits in the Configuration register to prohibit write operations to the Block Protection and Configuration registers. The WP# pin function only works in SPI single-bit and dual-bit read mode when the IOC bit in the Configuration register is set to '0'.

The WP# pin function is disabled when the WPEN bit in the Configuration register is '0'. This allows installation of SST26VF016B in a system with a grounded WP# pin while still enabling Write to the Block Protection register. The Lock-Down function of the Block Protection register supersedes the WP# pin. See Table 4-1 for Write Protection Lock-Down states.

The factory default setting at power-up of the WPEN bit is '0', disabling the Write-Protect function of the WP# after power-up. WPEN is a nonvolatile bit; once the bit is set to '1', the Write-Protect function of the WP# pin continues to be enabled after power-up. The WP# pin only protects the Block Protection register and Configuration register from changes. Therefore, if the WP# pin is set to low before or after a Program or Erase command or while an internal Write is in progress, it will have no effect on the Write command.

The IOC bit takes priority over the WPEN bit in the Configuration register. When the IOC bit is '1', the function of the WP# pin is disabled and the WPEN bit serves no function. When the IOC bit is '0' and WPEN is '1', setting the WP# pin active-low prohibits Write operations to the Block Protection Register.

WP#	IOC	WPEN	WPLD	Execute WBPR Instruction	Configuration Register
L	0	1	1	Not Allowed	Protected
L	0	0	1	Not Allowed	Writable
L	0	1	0	Not Allowed	Protected
L	O ⁽¹⁾	O ⁽²⁾	0	Allowed	Writable
Н	0	Х	1	Not Allowed	Writable
Н	0	Х	0	Allowed	Writable
Х	1	Х	1	Not Allowed	Writable
Х	1	O ⁽²⁾	0	Allowed	Writable

TABLE 4-1: WRITE PROTECTION LOCK-DOWN STATES

Note 1: Default at power-up register settings.

2: Factory default setting is '0'. This is a nonvolatile bit; default at power-up is the value set prior to power-down.

4.3 Security ID

SST26VF016B offers a 2-Kbyte Security ID (Sec ID) feature. The Security ID space is divided into two parts: one factory-programmed, 64-bit segment and one user-programmable segment.

The factory-programmed segment is programmed during part manufacture with a unique number and cannot be changed. The user-programmable segment is left unprogrammed for the customer to program as desired.

Use the Program Security ID (PSID) command to program the Security ID using the address shown in Table 5-5. The Security ID can be locked using the Lockout Security ID (LSID) command. This prevents any future write operations to the Security ID.

The factory-programmed portion of the Security ID cannot be programmed by the user; neither the factory-programmed nor user-programmable areas can be erased.

4.4 Hold Operation

The HOLD# pin pauses active serial sequences without resetting the clocking sequence. This pin is active after every power up and only operates during SPI single-bit and dual-bit modes.

SST26VF016B ships with the IOC bit set to '0' and the HOLD# pin function enabled. The HOLD# pin is always disabled in SQI mode and only works in SPI single-bit and dual-bit read mode.

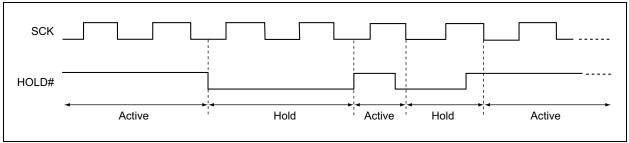
To activate the Hold mode, CE# must be in active-low state. The Hold mode begins when the SCK active-low state coincides with the falling edge of the HOLD# signal. The Hold mode ends when the HOLD# signal's rising edge coincides with the SCK active-low state.

If the falling edge of the HOLD# signal does not coincide with the SCK active-low state, then the device enters Hold mode when the SCK next reaches the active-low state. Similarly, if the rising edge of the HOLD# signal does not coincide with the SCK active-low state, then the device exits Hold mode when the SCK next reaches the active-low state (see Figure 4-3).

Once the device enters Hold mode, SO will be in high impedance state while SI and SCK can be VIL or VIH.

If CE# is driven active-high during a Hold condition, it resets the internal logic of the device. As long as HOLD# signal is low, the memory remains in the Hold condition. To resume communication with the device, HOLD# must be driven active-high, and CE# must be driven active-low.





4.5 STATUS Register

The STATUS register is a read-only register that provides the following status information: whether the Flash memory array is available for any Read or Write operation, if the device is write-enabled, whether an erase or program operation is suspended and if the Block Protection register and/or Security ID are locked down. During an internal Erase or Program operation, the STATUS register may be read to determine the completion of an operation in progress. Table 4-2 describes the function of each bit in the STATUS register.

TABLE 4-2: STATUS REGISTER

Bit	Name	Function	Default at Power-up	Read/Write (R/W)
0	BUSY	Write operation status 1 = Internal Write operation is in progress 0 = No internal Write operation is in progress	0	R
1	WEL	Write Enable Latch status 1 = Device is write-enabled 0 = Device is not write-enabled	0	R
2	WSE	Write Suspend Erase status 1 = Erase suspended 0 = Erase is not suspended	0	R
3	WSP	Write Suspend Program status 1 = Program suspended 0 = Program is not suspended	0	R
4	WPLD	Write Protection Lock-Down status 1 = Write Protection Lock-Down enabled 0 = Write Protection Lock-Down disabled	0	R
5	SEC ⁽¹⁾	Security ID status 1 = Security ID space locked 0 = Security ID space not locked	0(1)	R
6	RES	Reserved for future use	0	R
7	BUSY	Write operation status 1 = Internal Write operation is in progress 0 = No internal Write operation is in progress	0	R

Note 1: The Security ID status will always be '1' at power-up after a successful execution of the Lockout Security ID instruction, otherwise default at power-up is '0'.

4.5.1 WRITE-ENABLE LATCH (WEL)

The Write Enable Latch (WEL) bit indicates the status of the internal memory's Write Enable Latch. If the WEL bit is set to '1', the device is write enabled. If the bit is set to '0' (reset), the device is not write enabled and does not accept any memory Program or Erase, Protection Register Write or Lock-Down commands. The Write Enable Latch bit is automatically reset under the following conditions:

- · Power-up
- Reset
- Write Disable (WRDI) instruction
- · Page Program instruction completion
- · Sector Erase instruction completion
- · Block Erase instruction completion
- · Chip Erase instruction completion
- · Write Block Protection register instruction
- Lock-Down Block Protection register instruction
- · Program Security ID instruction completion
- · Lockout Security ID instruction completion
- · Write Suspend instruction
- · SPI Quad Page program instruction completion
- · Write STATUS Register

4.5.2 WRITE SUSPEND ERASE STATUS (WSE)

The Write Suspend Erase status (WSE) indicates when an erase operation has been suspended. The WSE bit is '1' after the host issues a suspend command during an erase operation. Once the suspended erase resumes, the WSE bit is reset to '0'.

4.5.3 WRITE SUSPEND PROGRAM STATUS (WSP)

The Write Suspend Program status (WSP) bit indicates when a program operation has been suspended. The WSP is '1' after the host issues a suspend command during the Program operation. Once the suspended Program resumes, the WSP bit is reset to '0'.

4.5.4 WRITE PROTECTION LOCK-DOWN STATUS (WPLD)

The Write Protection Lock-Down status (WPLD) bit indicates when the Block Protection register is locked down to prevent changes to the protection settings. The WPLD is '1' after the host issues a Lock-Down Block Protection command. After a power cycle, the WPLD bit is reset to '0'.

4.5.5 SECURITY ID STATUS (SEC)

The Security ID Status (SEC) bit indicates when the Security ID space is locked to prevent a write command. The SEC is '1' after the host issues a Lockout SID command. Once the host issues a Lockout SID command, the SEC bit can never be reset to '0.'

4.5.6 BUSY

The Busy bit determines whether there is an internal erase or program operation in progress. If the BUSY bit is '1', the device is busy with an internal erase or program operation. If the bit is '0', no erase or program operation is in progress.

4.6 Configuration Register

The Configuration register is a Read/Write register that stores a variety of configuration information. See Table 4-3 for the function of each bit in the register.

TABLE 4-3: CONFIGURATION REGISTER

Bit	Name	Function	Default at Power-up	Read/Write (R/W)
0	RES	Reserved	0	R
1	IOC	I/O Configuration for SPI Mode 1 = WP# and HOLD# pins disabled 0 = WP# and HOLD# pins enabled	₀ (1)	R/W
2	RES	Reserved	0	R
3	BPNV	Block Protection Volatility State 1 = No memory block has been permanently locked 0 = Any block has been permanently locked	1	R
4	RES	Reserved	0	R
5	RES	Reserved	0	R
6	RES	Reserved	0	R

Note 1: Default at Power-up is '0'.

2: Factory default setting. This is a nonvolatile bit; default at power-up will be the setting prior to power-down.

TABLE 4-3: CONFIGURATION REGISTER (CONTINUED)

Bit	Name	Function	Default at Power-up	Read/Write (R/W)
7	WPEN	Write-Protection Pin (WP#) Enable 1 = WP# enabled 0 = WP# disabled	O ⁽²⁾	R/W

Note 1: Default at Power-up is '0'.

2: Factory default setting. This is a nonvolatile bit; default at power-up will be the setting prior to power-down.

4.6.1 I/O CONFIGURATION (IOC)

The I/O Configuration (IOC) bit re-configures the I/O pins. The IOC bit is set by writing a '1' to Bit 1 of the Configuration register. When IOC bit is '0', the WP# pin and HOLD# pin are enabled (SPI or Dual Configuration setup). When IOC bit is set to '1', the SIO2 pin and SIO3 pin are enabled (SPI Quad I/O Configuration setup). The IOC bit must be set to '1' before issuing the following SPI commands: SQOR (6BH), SQIOR (EBH), RBSPI (ECH) and SPI Quad page program (32H). Without setting the IOC bit to '1', those SPI commands are not valid. The I/O configuration bit does not apply when in SQI mode. The default at power-up is '0'.

4.6.2 BLOCK PROTECTION VOLATILITY STATE (BPNV)

The Block Protection Volatility State bit indicates whether any block has been permanently locked with the Nonvolatile Write Lock Lock-Down register (nVWLDR). When no bits in the nVWLDR have been set, the BPNV is '1'; this is the default state from the factory. When one or more bits in the nVWLDR are set to '1', the BPNV bit will be '0' from that point forward, even after power-up.

4.6.3 WRITE-PROTECT ENABLE (WPEN)

The Write-Protect Enable (WPEN) bit is a nonvolatile bit that enables the WP# pin.

The Write-Protect (WP#) pin and the Write-Protect Enable (WPEN) bit control the programmable hardware write-protect feature. Setting the WP# pin to low and the WPEN bit to '1' enable hardware write protection. To disable hardware write protection, set either the WP# pin to high or the WPEN bit to '0'. There is latency associated with writing to the WPEN bit. Poll the BUSY bit in the STATUS register or wait TWPEN for the completion of the internal, self-timed write operation. When the chip is hardware write-protected, only write operations to Block Protection and Configuration registers are disabled. See Section 4.2 "Hardware Write Protection" and Table 4-1 for more information about the functionality of the WPEN bit.

5.0 INSTRUCTIONS

Instructions are used to read, write (erase and program) and configure the SST26VF016B. The complete list of the instructions is provided in Table 5-1.

TABLE 5-1: DEVICE OPERATION INSTRUCTIONS FOR SST26VF016B

Instruction	Description	Command	Мо	de	Address	Dummy	Data	Max	
mstruction	Description	Cycle ⁽¹⁾ SPI SQI		SQI	Cycle(s) ^(2,3) Cycle(s)		Cycle(s) ⁽³⁾	Freq ⁽⁴⁾	
Configuration	Configuration								
NOP	No Operation	00H	Χ	Х	0	0	0		
RSTEN	Reset Enable	66H	Χ	Х	0	0	0		
RST ⁽⁵⁾	Reset Memory	99H	Χ	Χ	0	0	0		
EQIO	Enable Quad I/O	38H	Х		0	0	0		
RSTQIO ⁽⁶⁾	Reset Quad I/O	FFH	Х	Х	0	0	0	104 MHz/	
DDCD	Read STATUS Register	05H	Х		0	0	1 to ∞	80 MHz	
RDSR	Read STATUS Register	USH		Х	0	1	1 to ∞		
WRSR	Write STATUS Register	01H	Х	Х	0	0	2	2	
DDCD	Read Configuration Register	35H	Х		0	0	1 to ∞		
RDCR		3311		Х	0	1	1 to ∞		
Read									
READ	Read Memory	03H	Χ		3	0	1 to ∞	40 MHz	
High-Speed	Read Memory at	0BH		Х	3	3	1 to ∞		
Read	Higher Speed	UDIT	Х		3	1	1 to ∞	404 8411 /	
SQOR ⁽⁷⁾	SPI Quad Output Read	6BH	Х		3	1	1 to ∞	104 MHz/ 80 MHz	
SQIOR ⁽⁸⁾	SPI Quad I/O Read	EBH	Х		3	3	1 to ∞	OO WII IZ	
SDOR ⁽⁹⁾	SPI Dual Output Read	3BH	Χ		3	1	1 to ∞		
SDIOR ⁽¹⁰⁾	SPI Dual I/O Read	BBH	Х		3	1	1 to ∞	80 MHz	
SB	Set Burst Length	C0H	Х	Х	0	0	1	404 144 1	
RBSQI	SQI Read Burst with Wrap	0CH		Х	3	3	n to ∞	104 MHz/ 80 MHz	
RBSPI ⁽⁸⁾	SPI Read Burst with Wrap	ECH	Х		3	3	n to ∞	OU IVII IZ	

- Note 1: Command cycle is two-clock periods in SQI mode and eight-clock periods in SPI mode.
 - 2: Address bits above the Most Significant bit of each density can be VIL or VIH.
 - Address, Dummy/Mode bits and Data cycles are two-clock periods in SQI and eight-clock periods in SPI mode.
 - **4:** The maximum frequency for all instructions is up to 104 MHz from 2.7V to 3.6V and up to 80 MHz from 2.3V to 3.6V unless otherwise noted. For extended temperature (+125°C), the maximum frequency is up to 80 MHz.
 - 5: RST command only executed if RSTEN command is executed first. Any intervening command will disable Reset.
 - 6: Device accepts eight-clock command in SPI mode or two-clock command in SQI mode.
 - 7: Data cycles are two-clock periods. IOC bit must be set to '1' before issuing the command.
 - **8:** Address, Dummy/Mode bits and data cycles are two-clock periods. IOC bit must be set to '1' before issuing the command.
 - 9: Data cycles are four-clock periods.
 - 10: Address, Dummy/Mode bits and Data cycles are four-clock periods.
 - 11: Sector Addresses: Use AMS-A12, remaining address are "don't care", but must be set to VIL or VIH.
 - **12:** Blocks are 64-Kbyte, 32-Kbyte or 8-Kbyte, depending on location. Block Erase Address: Ams-A₁₆ for 64-Kbyte; Ams-A₁₅ for 32-Kbyte; Ams-A₁₃ for 8-Kbyte. Remaining addresses are "don't care", but must be set to VIL or VIH.

TABLE 5-1: DEVICE OPERATION INSTRUCTIONS FOR SST26VF016B (CONTINUED)

Instruction	Description	Command Cycle ⁽¹⁾	Мо	de	Address	Dummy	Data	Max
instruction	struction Description		SPI	SQI	Cycle(s) ^(2,3)	Cycle(s) ⁽³⁾	Cycle(s) ⁽³⁾	Freq ⁽⁴⁾
Identification								
JEDEC-ID	JEDEC-ID Read	9FH	Х		0	0	3 to ∞	
Quad J-ID	Quad I/O J-ID Read	AFH		Х	0	1	3 to ∞	104 MHz/
SFDP	Serial Flash Discoverable Parameters	5AH	Х		3	1	1 to ∞	80 MHz
Write								
WREN	Write Enable	06H	Х	Х	0	0	0	
WRDI	Write Disable	04H	Х	Х	0	0	0	
SE (¹¹⁾	Erase 4 Kbytes of Memory Array	20H	Х	Х	3	0	0	
BE(12)	Erase 64, 32 or 8 Kbytes of Memory Array	D8H	Х	Х	3	0	0	104 MHz/ 80 MHz
CE	Erase Full Array	C7H	Х	Х	0	0	0	
PP	Page Program	02H	Х	Х	3	0	1 to 256	
SPI Quad PP ⁽⁷⁾	SQI Quad Page Program	32H	Х		3	0	1 to 256	
WRSU	Suspends Program/Erase	В0Н	Х	Х	0	0	0	104 MHz/
WRRE	Resumes Program/Erase	30H	Х	Х	0	0	0	80 MHz

- Note 1: Command cycle is two-clock periods in SQI mode and eight-clock periods in SPI mode.
 - 2: Address bits above the Most Significant bit of each density can be VIL or VIH.
 - 3: Address, Dummy/Mode bits and Data cycles are two-clock periods in SQI and eight-clock periods in SPI mode.
 - **4:** The maximum frequency for all instructions is up to 104 MHz from 2.7V to 3.6V and up to 80 MHz from 2.3V to 3.6V unless otherwise noted. For extended temperature (+125°C), the maximum frequency is up to 80 MHz.
 - 5: RST command only executed if RSTEN command is executed first. Any intervening command will disable Reset.
 - **6:** Device accepts eight-clock command in SPI mode or two-clock command in SQI mode.
 - 7: Data cycles are two-clock periods. IOC bit must be set to '1' before issuing the command.
 - **8:** Address, Dummy/Mode bits and data cycles are two-clock periods. IOC bit must be set to '1' before issuing the command.
 - 9: Data cycles are four-clock periods.
 - 10: Address, Dummy/Mode bits and Data cycles are four-clock periods.
 - 11: Sector Addresses: Use AMS-A12, remaining address are "don't care", but must be set to VIL or VIH.
 - **12:** Blocks are 64-Kbyte, 32-Kbyte or 8-Kbyte, depending on location. Block Erase Address: Ams-A₁₆ for 64-Kbyte; Ams-A₁₅ for 32-Kbyte; Ams-A₁₃ for 8-Kbyte. Remaining addresses are "don't care", but must be set to VIL or VIH.

TABLE 5-1: DEVICE OPERATION INSTRUCTIONS FOR SST26VF016B (CONTINUED)

Instruction	Description	Command	Мо	de	Address	Dummy	Data	Max	
instruction	Description	Cycle ⁽¹⁾	SPI	SQI	Cycle(s) ^(2,3)	Cycle(s) ⁽³⁾	Cycle(s) ⁽³⁾	Freq ⁽⁴⁾	
Protection	Protection								
RBPR	Read Block Protection	72H	Х		0	0	1 to 6		
	Register			Χ	0	1	1 to 6		
WBPR	Write Block Protection Register	42H	Х	х	0	0	1 to 6		
LBPR	Lock Down Block Protection Register	8DH	Х	Х	0	0	0		
nVWLDR	Nonvolatile Write Lock-Down Register	E8H	Х	Х	0	0	1 to 6	104 MHz/	
ULBPR	Global Block Protection Unlock	98H	Х	Х	0	0	0	80 MHz	
DOTE	Dood Coought ID	88H	Х		2	1	1 to 2048		
RSID	Read Security ID	ООП		Х	2	3	1 to 2048		
PSID	Program User Security ID area	A5H	Х	Х	2	0	1 to 256		
LSID	Lockout Security ID Programming	85H	Х	Х	0	0	0		
Power Savir	ng								
DPD	Deep Power-Down Mode	В9Н	Х	Х	0	0	0	104 MH-/	
RDPD	Release from Deep Power-Down and Read ID	ABH	Х	Х	3	0	1 to ∞	104 MHz/ 80 MHz	

- Note 1: Command cycle is two-clock periods in SQI mode and eight-clock periods in SPI mode.
 - 2: Address bits above the Most Significant bit of each density can be VIL or VIH.
 - Address, Dummy/Mode bits and Data cycles are two-clock periods in SQI and eight-clock periods in SPI mode.
 - **4:** The maximum frequency for all instructions is up to 104 MHz from 2.7V to 3.6V and up to 80 MHz from 2.3V to 3.6V unless otherwise noted. For extended temperature (+125°C), the maximum frequency is up to 80 MHz.
 - 5: RST command only executed if RSTEN command is executed first. Any intervening command will disable Reset.
 - 6: Device accepts eight-clock command in SPI mode or two-clock command in SQI mode.
 - 7: Data cycles are two-clock periods. IOC bit must be set to '1' before issuing the command.
 - **8:** Address, Dummy/Mode bits and data cycles are two-clock periods. IOC bit must be set to '1' before issuing the command.
 - 9: Data cycles are four-clock periods.
 - 10: Address, Dummy/Mode bits and Data cycles are four-clock periods.
 - 11: Sector Addresses: Use Ams-A12, remaining address are "don't care", but must be set to VIL or VIH.
 - **12:** Blocks are 64-Kbyte, 32-Kbyte or 8-Kbyte, depending on location. Block Erase Address: Ams-A₁₆ for 64-Kbyte; Ams-A₁₅ for 32-Kbyte; Ams-A₁₃ for 8-Kbyte. Remaining addresses are "don't care", but must be set to VIL or VIH.

5.1 No Operation (NOP)

The No Operation command only cancels a Reset Enable command. ${\tt NOP}$ has no impact on any other command.

5.2 Reset Enable (RSTEN) and Reset (RST)

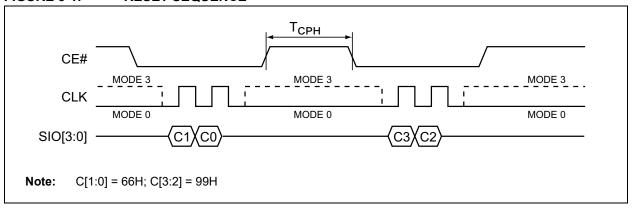
The Reset operation is used as a system (software) reset that puts the device in normal operating Ready mode. This operation consists of two commands: Reset Enable (RSTEN) followed by Reset (RST).

To reset SST26VF016B, the host drives CE# low, sends the Reset Enable command (66H) and drives CE# high. Next, the host drives CE# low again, sends the Reset command (99H) and drives CE# high (see Figure 5-1).

The Reset operation requires the Reset Enable command followed by the Reset command. Any command other than the Reset command after the Reset Enable command will disable the Reset Enable.

Once the Reset Enable and Reset commands are successfully executed, the device returns to normal operation Read mode and then does the following: resets the protocol to SPI mode, resets the burst length to 8 bytes, clears all the bits, except for bit 4 (WPLD) and bit 5 (SEC) in the STATUS register to their default states, and clears bit 1 (IOC) in the Configuration register to its default state. A device Reset during an active program or erase operation aborts the operation, which can cause the data of the targeted address range to be corrupted or lost. Depending on the prior operation, the Reset timing may vary. Recovery from a write operation requires more latency time than recovery from other operations. See Table 8-2 for Rest timing parameters.

FIGURE 5-1: RESET SEQUENCE



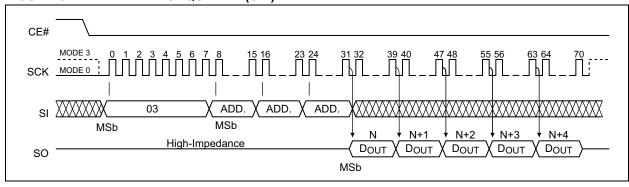
5.3 Read (40 MHz)

The READ instruction, 03H, is supported in SPI bus protocol only with clock frequencies up to 40 MHz. This command is not supported in SQI bus protocol. The device outputs the data starting from the specified address location, then continuously streams the data output through all addresses until terminated by a low-to-high transition on CE#.

The internal Address Pointer will automatically increment until the highest memory address is reached. Once the highest memory address is reached, the Address Pointer will automatically return to the beginning (wrap-around) of the address space.

Initiate the READ instruction by executing an 8-bit command, 03H, followed by address bits A[23:0]. CE# must remain active-low for the duration of the Read cycle. See Figure 5-2 for Read Sequence.

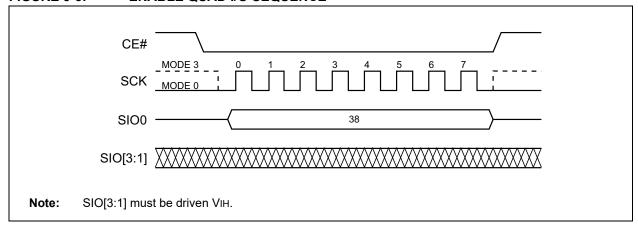
FIGURE 5-2: READ SEQUENCE (SPI)



5.4 Enable Quad I/O (EQIO)

The Enable Quad I/O (EQIO) instruction, 38H, enables the Flash device for SQI bus operation. Upon completion of the instruction, all instructions thereafter are expected to be 4-bit multiplexed input/output (SQI mode) until a power cycle or a "Reset Quad I/O instruction" is executed (see Figure 5-3).

FIGURE 5-3: ENABLE QUAD I/O SEQUENCE



5.5 Reset Quad I/O (RSTQIO)

The Reset Quad I/O instruction, FFH, resets the device to 1-bit SPI protocol operation or exits the Set Mode configuration during a read sequence. This command allows the Flash device to return to the default I/O state (SPI) without a power cycle and executes in either 1-bit or 4-bit mode. If the device is in the Set Mode configuration, while in SQI High-Speed Read mode, the RSTQIO command will only return the device to a state where it can accept new command instruction. An additional RSTQIO is required to reset the device to SPI mode.

To execute a Reset Quad I/O operation, the host drives CE# low, sends the Reset Quad I/O command cycle (FFH), then drives CE# high. Execute the instruction in either SPI (8 clocks) or SQI (2 clocks) command cycles. For SPI, SIO[3:1] are "don't care" for this command, but should be driven to VIH or VIL (see Figure 5-4 and Figure 5-5).

FIGURE 5-4: RESET QUAD I/O SEQUENCE (SPI)

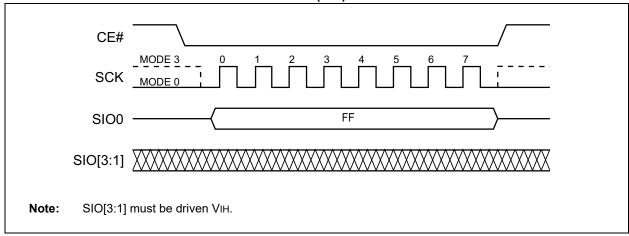
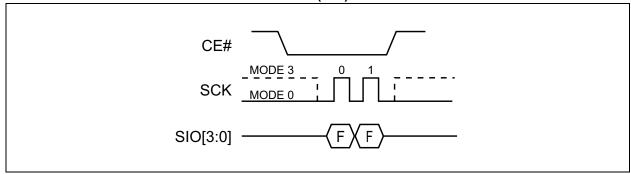


FIGURE 5-5: RESET QUAD I/O SEQUENCE (SQI)

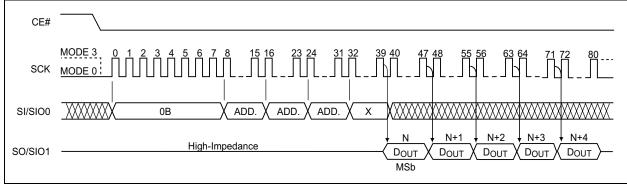


5.6 High-Speed Read

The High-Speed Read instruction, 0BH, is supported in both SPI bus protocol and SQI protocol. This instruction supports frequencies of up to 80 MHz or 104 MHz with additional dummy input cycles prior to first data byte output. On power-up, the device is set to use SPI.

Initiate High-Speed Read by executing an 8-bit command, 0BH, followed by address bits A[23-0] and a dummy byte. CE# must remain active-low for the duration of the High-Speed Read cycle. See Figure 5-6 for the High-Speed Read sequence for SPI bus protocol.

FIGURE 5-6: HIGH-SPEED READ SEQUENCE (SPI) (C[1:0] = 0BH)



In SQI protocol, the host drives CE# low then sends one High-Speed Read command cycle, 0BH, followed by three address cycles, a Set Mode Configuration cycle and two dummy cycles. Each cycle is two nibbles (clocks) long, most significant nibble first.

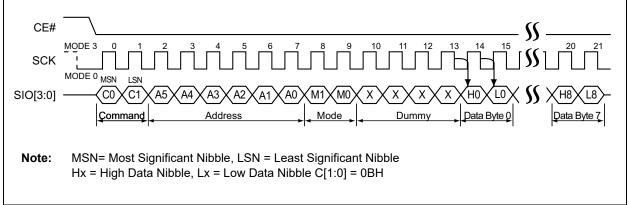
After the dummy cycles, the device outputs data on the falling edge of the SCK signal starting from the specified address location. The device continually streams data output through all addresses until terminated by a low-to-high transition on CE#. The internal Address Pointer automatically increments until the highest memory address is reached, at which point the Address Pointer returns to address location 000000H. During this operation, blocks that are Read-locked will output data 00H.

The Set Mode Configuration bit M[7:0] indicates if the next instruction cycle is another SQI High-Speed Read command. When M[7:0] = AXH, the device expects the next continuous instruction to be another Read command, 0BH, and does not require the op-code to be entered again.

The host may initiate the next Read cycle by driving CE# low, then sending the four-bit input for address A[23:0], followed by the Set Mode configuration bits M[7:0] and two dummy cycles. After the two dummy cycles, the device outputs the data starting from the specified address location. There are no restrictions on address location access.

When M[7:0] is any value other than AXH, the device expects the next instruction initiated to be a command instruction. To reset/exit the Set Mode configuration, execute the Reset Quad I/O command, FFH. While in the Set Mode configuration, the RSTQIO command will only return the device to a state where it can accept new command instruction. An additional RSTQIO is required to reset the device to SPI mode. See Figure 5-10 for the SPI Quad I/O Mode Read sequence when M[7:0] = AXH.



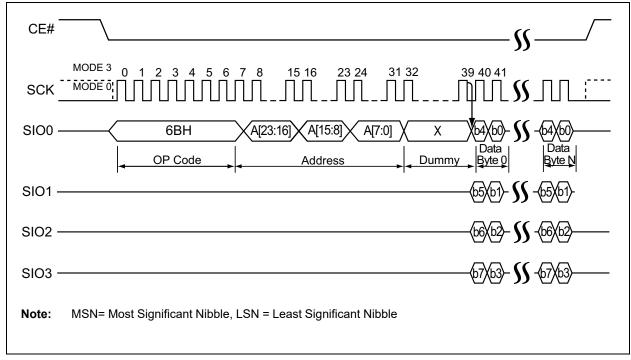


5.7 SPI Quad Output Read

The SPI Quad Output Read instruction supports frequencies of up to 80 MHz or 104 MHz with additional dummy input cycles prior to first data byte output. SST26VF016B requires the IOC bit in the Configuration register to be set to '1' prior to executing the command. Initiate SPI Quad Output Read by executing an 8-bit command, 6BH, followed by address bits A[23-0] and a dummy byte. CE# must remain active-low for the duration of the SPI Quad Mode Read. See Figure 5-8 for the SPI Quad Output Read sequence.

Following the dummy byte, the device outputs data from SIO[3:0] starting from the specified address location. The device continually streams data output through all addresses until terminated by a low-to-high transition on CE#. The internal Address Pointer automatically increments until the highest memory address is reached, at which point the Address Pointer returns to the beginning of the address space.

FIGURE 5-8: SPI QUAD OUTPUT READ



5.8 SPI Quad I/O Read

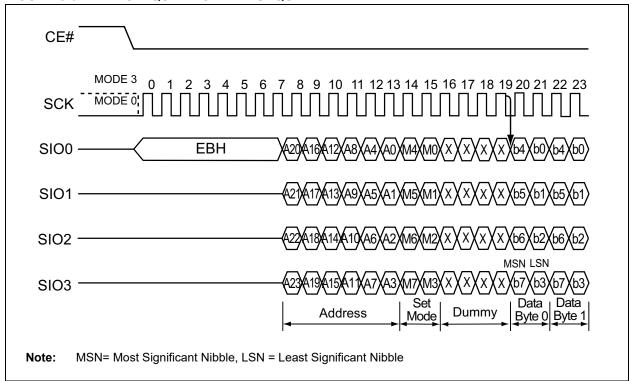
The SPI Quad I/O Read (SQIOR) instruction supports frequencies of up to 80 MHz or 104 MHz with additional dummy input cycles prior to first data byte output. SST26VF016B requires the IOC bit in the Configuration register to be set to '1' prior to executing the command. Initiate SQIOR by executing an 8-bit command, EBH. The device then switches to 4-bit I/O mode for address bits A[23-0], followed by the Set Mode configuration bits M[7:0] and two dummy bytes. CE# must remain active-low for the duration of the SPI Quad I/O Read. See Figure 5-9 for the SPI Quad I/O Read sequence.

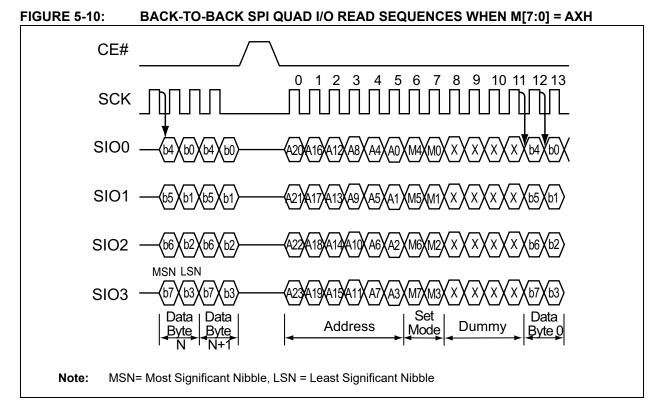
Following the dummy bytes, the device outputs data from the specified address location. The device continually streams data output through all addresses until terminated by a low-to-high transition on CE#. The internal Address Pointer automatically increments until the highest memory address is reached, at which point the Address Pointer returns to the beginning of the address space.

The Set Mode Configuration bit M[7:0] indicates if the next instruction cycle is another SPI Quad I/O Read command. When M[7:0] = AXH, the device expects the next continuous instruction to be another Read command (EBH) and does not require the op-code to be entered again. The host may set the next SQIOR cycle by driving CE# low, then sending the four-bit wide input for address A[23:0], followed by the Set Mode configuration bits M[7:0] and two dummy cycles. After the two dummy cycles, the device outputs the data starting from the specified address location. There are no restrictions on address location access.

When M[7:0] is any value other than AXH, the device expects the next instruction initiated to be a command instruction. To reset/exit the Set Mode configuration, execute the Reset Quad I/O command (FFH). See Figure 5-10 for the SPI Quad I/O Mode Read sequence when M[7:0] = AXH.

FIGURE 5-9: SPI QUAD I/O READ SEQUENCE





5.9 Set Burst

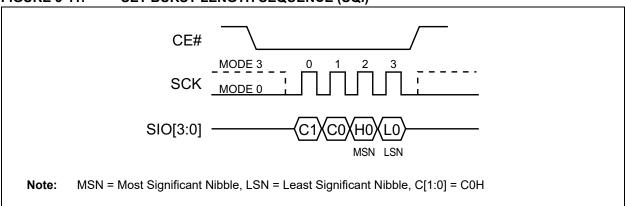
The Set Burst command specifies the number of bytes to be output during a Read Burst command before the device wraps around. It supports both SPI and SQI protocols. To set the burst length, the host drives CE# low, sends the Set Burst command cycle (C0H) and one data cycle, then drives CE# high.

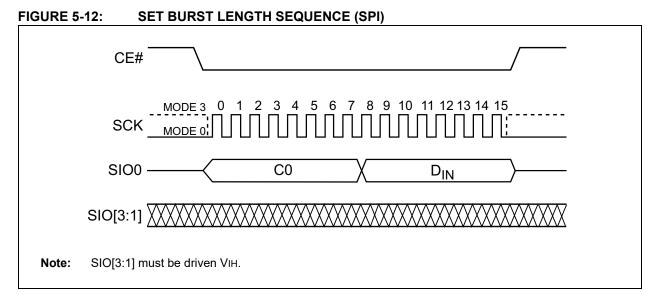
After power-up or Reset, the burst length is set to eight bytes (00H). See Table 5-2 for burst length data and Figures 5-11 and 5-12 for the sequences.

TABLE 5-2: BURST LENGTH DATA

Burst Length	High Nibble (H0)	Low Nibble (L0)
8 Bytes	0h	0h
16 Bytes	0h	1h
32 Bytes	0h	2h
64 Bytes	0h	3h

FIGURE 5-11: SET BURST LENGTH SEQUENCE (SQI)





5.10 SQI Read Burst with Wrap (RBSQI)

SQI Read Burst with wrap is similar to High-Speed Read in SQI mode, except data will output continuously within the burst length until a low-to-high transition on CE#. To execute a SQI Read Burst operation, drive CE# low, then send the Read Burst command cycle (0CH), followed by three address cycles and then three dummy cycles. Each cycle is two nibbles (clocks) long, most significant nibble first.

After the dummy cycles, the device outputs data on the falling edge of the SCK signal starting from the specified address location. The data output stream is continuous through all addresses until terminated by a low-to-high transition on CE#.

During RBSQI, the internal Address Pointer automatically increments until the last byte of the burst is reached, then it wraps around to the first byte of the burst. All bursts are aligned to addresses within the burst length (see Table 5-3). For example, if the burst length is eight bytes and the start address is 06h, the burst sequence would be: 06h, 07h, 00h, 01h, 02h, 03h, 04h, 05h, 06h, etc. The pattern repeats until the command is terminated by a low-to-high transition on CF#

During this operation, blocks that are read-locked will output data 00H.

5.11 SPI Read Burst with Wrap (RBSPI)

SPI Read Burst with Wrap (RBSPI) is similar to SPI Quad I/O Read except the data will output continuously within the burst length until a low-to-high transition on CE#. To execute a SPI Read Burst with Wrap operation, drive CE# low, then send the Read Burst command cycle (ECH), followed by three address cycles and then three dummy cycles.

After the dummy cycle, the device outputs data on the falling edge of the SCK signal starting from the specified address location. The data output stream is continuous through all addresses until terminated by a low-to-high transition on CE#.

During RBSPI, the internal Address Pointer automatically increments until the last byte of the burst is reached, then it wraps around to the first byte of the burst. All bursts are aligned to addresses within the burst length (see Table 5-3). For example, if the burst length is eight bytes and the start address is 06h, the burst sequence would be: 06h, 07h, 00h, 01h, 02h, 03h, 04h, 05h, 06h, etc. The pattern repeats until the command is terminated by a low-to-high transition on CE#.

During this operation, blocks that are read-locked will output data 00H.

TABLE 5-3: BURST ADDRESS RANGES

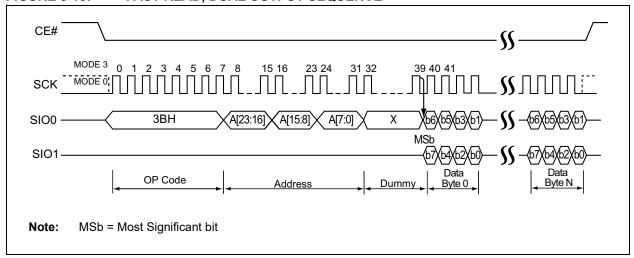
Burst Length	Burst Address Ranges
8 Bytes	00-07H, 08-0FH, 10-17H, 18-1FH
16 Bytes	00-0FH, 10-1FH, 20-2FH, 30-3FH
32 Bytes	00-1FH, 20-3FH, 40-5FH, 60-7FH
64 Bytes	00-3FH, 40-7FH, 80-BFH, C0-FFH

5.12 SPI Dual Output Read

The SPI Dual Output Read instruction supports frequencies of up to 80 MHz or 104 MHz with additional dummy input cycles prior to first data byte output. Initiate SPI Dual Output Read by executing an 8-bit command (3BH), followed by address bits A[23-0] and a dummy byte. CE# must remain active-low for the duration of the SPI Dual Output Read operation. See Figure 5-13 for the SPI Quad Output Read sequence.

Following the dummy byte, SST26VF016B outputs data from SIO[1:0] starting from the specified address location. The device continually streams data output through all addresses until terminated by a low-to-high transition on CE#. The internal Address Pointer automatically increments until the highest memory address is reached, at which point the Address Pointer returns to the beginning of the address space.

FIGURE 5-13: FAST READ, DUAL OUTPUT SEQUENCE



5.13 SPI Dual I/O Read

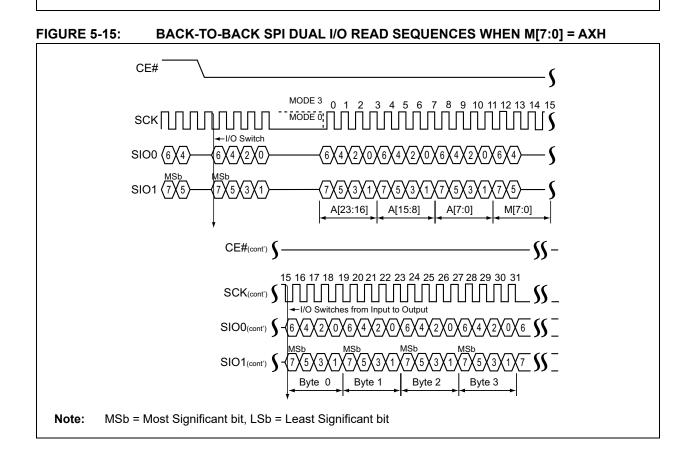
The SPI Dual I/O Read (SDIOR) instruction supports up to 80 MHz frequency. Initiate SDIOR by executing an 8-bit command (BBH). The device then switches to 2-bit I/O mode for address bits A[23-0], followed by the Set Mode configuration bits M[7:0]. CE# must remain active-low for the duration of the SPI Dual I/O Read. See Figure 5-14 for the SPI Dual I/O Read sequence.

Following the Set Mode configuration bits, the SST26VF016B outputs data from the specified address location. The device continually streams data output through all addresses until terminated by a low-to-high transition on CE#. The internal Address Pointer automatically increments until the highest memory address is reached, at which point the Address Pointer returns to the beginning of the address space.

The Set Mode Configuration bit M[7:0] indicates if the next instruction cycle is another SPI Dual I/O Read command. When M[7:0] = AXH, the device expects the next continuous instruction to be another SDIOR command (BBH) and does not require the op-code to be entered again. The host may set the next SDIOR cycle by driving CE# low, then sending the two-bit wide input for address A[23:0], followed by the Set Mode configuration bits M[7:0]. After the Set Mode Configuration bits, the device outputs the data starting from the specified address location. There are no restrictions on address location access.

When M[7:0] is any value other than AXH, the device expects the next instruction initiated to be a command instruction. To reset/exit the Set Mode configuration, execute the Reset Quad I/O command (FFH). See Figure 5-15 for the SPI Dual I/O Read sequence when M[7:0] = AXH.

FIGURE 5-14: SPI DUAL I/O READ SEQUENCE CE# 5 6 7 8 9 10 11 12 13 14 15 16 17 18 19 20 21 22 23 SIO0 XXXX BBH SIO1 -A[23:16] A[15:8] CE#(cont') SCK(cont') SIO1(cont') \ -{7} Byte 0 Byte 1 Byte 2 Byte 3 MSb= Most Significant bit, LSb = Least Significant bit



Note:

5.14 JEDEC ID Read (SPI Protocol)

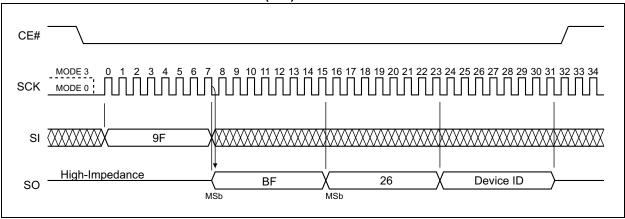
Using traditional SPI protocol, the JEDEC ID Read instruction identifies the device as SST26VF016B and the manufacturer as Microchip $^{\circledR}$. To execute a JECEC ID operation, the host drives CE# low, then sends the JEDEC ID command cycle (9FH).

Immediately following the command cycle, SST26VF016B output data on the falling edge of the SCK signal. The data output stream is continuous until terminated by a low-to-high transition on CE#. The device outputs three bytes of data: manufacturer, device type and device ID (see Table 5-4). See Figure 5-16 for instruction sequence.

TABLE 5-4: DEVICE ID DATA OUTPUT

Product	Manufacturer ID (Byte 1)	Device ID		
Product	Manufacturer ID (Byte 1)	Device Type (Byte 2)	Device ID (Byte 3)	
SST26VF016B	BFH	26H	41H	



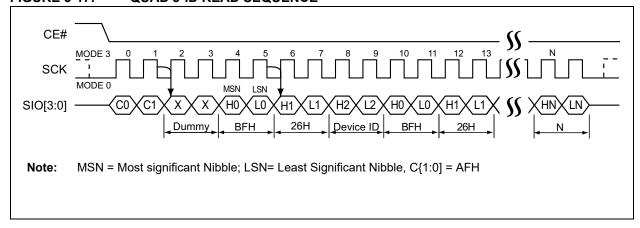


5.15 Read Quad J-ID Read (SQI Protocol)

The Read Quad J-ID Read instruction identifies the device as SST26VF016B and manufacturer as Microchip. To execute a Quad J-ID operation, the host drives CE# low and then sends the Quad J-ID command cycle (AFH). Each cycle is two nibbles (clocks) long, most significant nibble first.

Immediately following the command cycle and one dummy cycle, SST26VF016B outputs data on the falling edge of the SCK signal. The data output stream is continuous until terminated by a low-to-high transition of CE#. The device outputs three bytes of data: manufacturer, device type and device ID (see Table 5-4). See Figure 5-17 for instruction sequence.

FIGURE 5-17: QUAD J-ID READ SEQUENCE

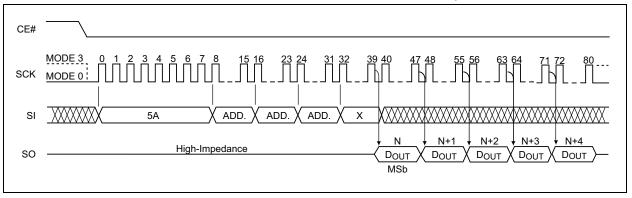


5.16 Serial Flash Discoverable Parameters (SFDP)

The Serial Flash Discoverable Parameters (SFDP) contain information describing the characteristics of the device. This allows device-independent, JEDEC ID-independent and forward/backward compatible software support for all future Serial Flash device families. See Table 11-1 for address and data values.

Initiate SFDP by executing an 8-bit command (5AH), followed by address bits A[23-0] and a dummy byte. CE# must remain active-low for the duration of the SFDP cycle. For the SFDP sequence, see Figure 5-18.

FIGURE 5-18: SERIAL FLASH DISCOVERABLE PARAMETERS SEQUENCE



5.17 Sector Erase

The Sector Erase instruction clears all bits in the selected 4 Kbyte sector to '1,' but it does not change a protected memory area. Prior to any write operation, the Write Enable (WREN) instruction must be executed.

To execute a Sector Erase operation, the host drives CE# low, then sends the Sector Erase command cycle (20H) and three address cycles and then drives CE# high.

Address bits [AMS-A12] (AMS = Most Significant Address) determine the sector address (SAX); the remaining address bits can be VIL or VIH. To identify the completion of the internal, self-timed, Write operation, poll the BUSY bit in the STATUS register or wait Tse. See Figures 5-19 and 5-20 for the Sector Erase sequence.

FIGURE 5-19: 4-KBYTE SECTOR ERASE SEQUENCE (SQI)

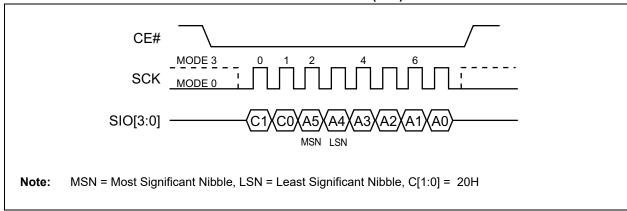
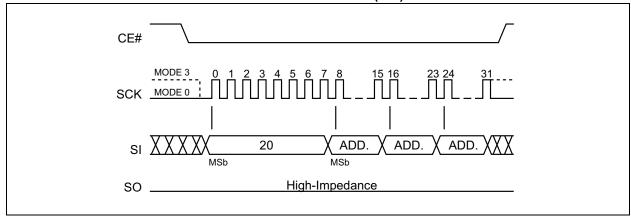


FIGURE 5-20: 4-KBYTE SECTOR ERASE SEQUENCE (SPI)



5.18 Block Erase

The Block Erase instruction clears all bits in the selected block to '1'. Block sizes can be 8-Kbyte, 32-Kbyte or 64-Kbyte depending on address (see Figure 3-1 for details. A Block Erase instruction applied to a protected memory area will be ignored. Prior to any write operation, execute the WREN instruction. Keep CE# active-low for the duration of any command sequence.

To execute a Block Erase operation, the host drives CE# low then sends the Block Erase command cycle (D8H), three address cycles, then drives CE# high. Address bits AMS-A13 determine the block address (BAx); the remaining address bits can be VIL or VIH. For 32-Kbyte blocks, A14-A13 can be VIL or VIH. For 64-Kbyte blocks, A15-A13 can be VIL or VIH. Poll the BUSY bit in the STATUS register or wait TBE, for the completion of the internal, self-timed, Block Erase operation. See Figures 5-21 and 5-22 for the Block Erase sequence.

FIGURE 5-21: BLOCK ERASE SEQUENCE (SQI)

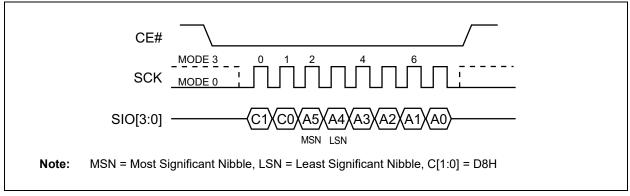
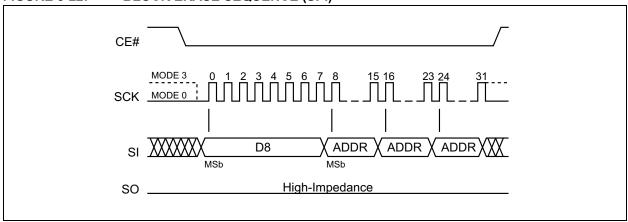


FIGURE 5-22: BLOCK ERASE SEQUENCE (SPI)

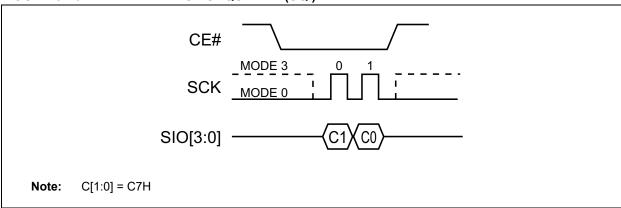


5.19 Chip Erase

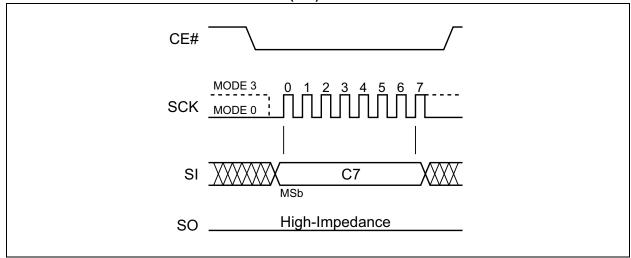
The Chip Erase instruction clears all bits in the device to '1.' The Chip Erase instruction is ignored if any of the memory area is protected. Prior to any write operation, execute the \mathtt{WREN} instruction.

To execute a Chip Erase operation, the host drives CE# low, sends the Chip Erase command cycle (C7H), then drives CE# high. Poll the BUSY bit in the STATUS register or wait TSCE for the completion of the internal, self-timed, Write operation. See Figures 5-23 and 5-24 for the Chip Erase sequence.

FIGURE 5-23: CHIP ERASE SEQUENCE (SQI)







5.20 Page Program

The Page Program instruction programs up to 256 bytes of data in the memory and supports both SPI and SQI protocols. The data for the selected page address must be in the erased state (FFH) before initiating the Page Program operation. A Page Program applied to a protected memory area will be ignored. Prior to the program operation, execute the $_{\rm WREN}$ instruction.

To execute a Page Program operation, the host drives CE# low, then sends the Page Program command cycle (02H), three address cycles followed by the data to be programmed, then drives CE# high. The programmed data must be between 1 to 256 bytes and in whole byte increments; sending less than a full byte will cause the partial byte to be ignored.

Poll the BUSY bit in the STATUS register or wait TPP for the completion of the internal, self-timed, Write operation. See Figures 5-25 and 5-26 for the Page Program sequence.

When executing Page Program, the memory range for the SST26VF016B is divided into 256-byte page boundaries. The device handles shifting of more than 256 bytes of data by maintaining the last 256 bytes of data as the correct data to be programmed. If the target address for the Page Program instruction is not the beginning of the page boundary (A[7:0] are not all zero) and the number of bytes of data input exceeds or overlaps the end of the address of the page boundary, the excess data inputs wrap around and will be programmed at the start of that target page.

FIGURE 5-25: PAGE PROGRAM SEQUENCE (SQI)

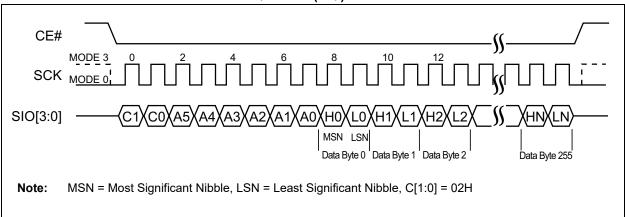
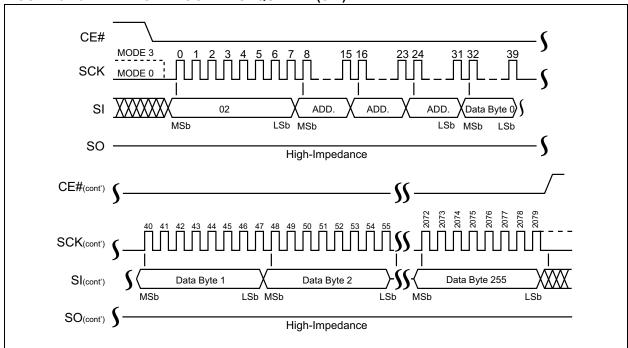


FIGURE 5-26: PAGE PROGRAM SEQUENCE (SPI)



5.21 SPI Quad Page Program

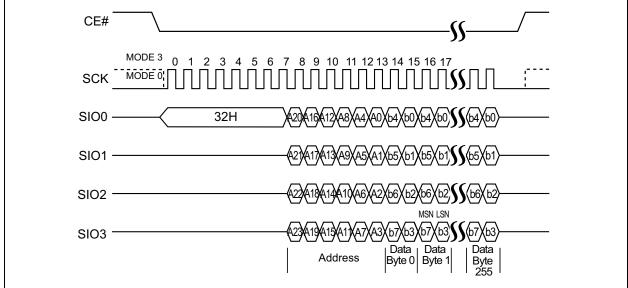
The SPI Quad Page Program instruction programs up to 256 bytes of data in the memory. The data for the selected page address must be in the erased state (FFH) before initiating the SPI Quad Page Program operation. A SPI Quad Page Program applied to a protected memory area will be ignored. SST26VF016B requires the ICO bit in the Configuration register to be set to '1' prior to executing the command. Prior to the program operation, execute the WREN instruction.

To execute a SPI Quad Page Program operation, the host drives CE# low, then sends the SPI Quad Page Program command cycle (32H), three address cycles followed by the data to be programmed, then drives CE# high. The programmed data must be between 1 to 256 bytes and in whole byte increments.

The command cycle is eight clocks long, the address and data cycles are each two clocks long, Most Significant bit first. Poll the BUSY bit in the STATUS register or wait TPP for the completion of the internal, self-timed, Write operation (see Figure 5-27).

When executing SPI Quad Page Program, the memory range for the SST26VF016B is divided into 256 byte page boundaries. The device handles shifting of more than 256 bytes of data by maintaining the last 256 bytes of data as the correct data to be programmed. If the target address for the SPI Quad Page Program instruction is not the beginning of the page boundary (A[7:0] are not all zero) and the of bytes of data input exceeds or overlaps the end of the address of the page boundary, the excess data inputs wrap around and will be programmed at the start of that target page.





5.22 Write Suspend and Write Resume

Write Suspend allows the interruption of Sector Erase, Block Erase, SPI Quad Page Program or Page Program operations in order to erase, program or read data in another portion of memory. The original operation can be continued with the Write Resume command. This operation is supported in both SQI and SPI protocols.

Only one write operation can be suspended at a time; if an operation is already suspended, the device will ignore the Write Suspend command. Write Suspend during Chip Erase is ignored; Chip Erase is not a valid command while a write is suspended. The Write Resume command is ignored until any write operation (Program or Erase) initiated during the Write Suspend is complete. The device requires a minimum of 500 µs between each Write Suspend command.

5.23 Write Suspend During Sector Erase or Block Erase

Issuing a Write Suspend instruction during Sector Erase or Block Erase allows the host to program or read any sector that was not being erased. The device will ignore any programming commands pointing to the suspended sector(s). Any attempt to read from the suspended sector(s) will output unknown data because the Sector or Block Erase will be incomplete.

To execute a Write Suspend operation, the host drives CE# low, sends the Write Suspend command cycle (B0H), then drives CE# high. The STATUS register indicates that the erase has been suspended by changing the WSE bit from '0' to '1,' but the device will not accept another command until it is ready. To determine when the device will accept a new command, poll the BUSY bit in the STATUS register or wait Tws.

5.24 Write Suspend During Page Programming or SPI Quad Page Programming

Issuing a Write Suspend instruction during Page Programming allows the host to erase or read any sector that is not being programmed. Erase commands pointing to the suspended sector(s) will be ignored. Any attempt to read from the suspended page will output unknown data because the program will be incomplete.

To execute a Write Suspend operation, the host drives CE# low, sends the Write Suspend command cycle (B0H), then drives CE# high. The STATUS register indicates that the programming has been suspended by changing the WSP bit from '0' to '1,' but the device will not accept another command until it is ready. To determine when the device will accept a new command, poll the BUSY bit in the STATUS register or wait Tws.

5.25 Write Resume

Write Resume restarts a write command that was suspended and changes the suspend status bit in the STATUS register (WSE or WSP) back to '0'.

To execute a Write Resume operation, the host drives CE# low, sends the Write Resume command cycle (30H), then drives CE# high. To determine if the internal, self-timed Write operation completed, poll the BUSY bit in the STATUS register or wait the specified time TSE, TBE or TPP for Sector Erase, Block Erase or Page Programming, respectively. The total write time before suspend and after resume will not exceed the uninterrupted write times TSE, TBE or TPP.

5.26 Read Security ID

The Read Security ID operation is supported in both SPI and SQI modes. To execute a Read Security ID (SID) operation in SPI mode, the host drives CE# low, sends the Read Security ID command cycle (88H), two address cycles and then one dummy cycle. To execute a Read Security ID operation in SQI mode, the host drives CE# low and then sends the Read Security ID command, two address cycles and three dummy cycles.

After the dummy cycles, the device outputs data on the falling edge of the SCK signal, starting from the specified address location. The data output stream is continuous through all SID addresses until terminated by a low-to-high transition on CE#. See Table 5-5 for the Security ID address range.

5.27 Program Security ID

The Program Security ID instruction programs one to 2040 bytes of data in the user-programmable, Security ID space. This Security ID space is One-Time-Programmable (OTP). The device ignores a Program Security ID instruction pointing to an invalid or protected address (see Table 5-5). Prior to the program operation, execute WREN.

To execute a Program SID operation, the host drives CE# low, sends the Program Security ID command cycle (A5H), two address cycles, the data to be programmed, then drives CE# high. The programmed data must be between 1 to 256 bytes and in whole byte increments.

The device handles shifting of more than 256 bytes of data by maintaining the last 256 bytes of data as the correct data to be programmed. If the target address for the Program Security ID instruction is not the beginning of the page boundary and the number of data input exceeds or overlaps the end of the address of the page boundary, the excess data inputs wrap around and will be programmed at the start of that target page.

The Program Security ID operation is supported in both SPI and SQI mode. To determine the completion of the internal, self-timed Program SID operation, poll the BUSY bit in the software STATUS register or wait TPSID for the completion of the internal self-timed Program Security ID operation.

TABLE 5-5: PROGRAM SECURITY ID

Program Security ID	Address Range
Unique ID Pre-Programmed at factory	0000-0007H
User Programmable	0008H-07FFH

5.28 Lockout Security ID

The Lockout Security ID instruction prevents any future changes to the Security ID and is supported in both SPI and SQI modes. Prior to the operation, execute WREN.

To execute a Lockout SID, the host drives CE# low, sends the Lockout Security ID command cycle (85H), then drives CE# high. Poll the BUSY bit in the software STATUS register or wait TPSID, for the completion of the Lockout Security ID operation.

5.29 Read Status Register (RDSR) and Read Configuration Register (RDCR)

The Read Status Register (RDSR) and Read Configuration Register (RDCR) commands output the contents of the STATUS and Configuration registers. These commands function in both SPI and SQI modes. The STATUS register may be read at any time, even during a write operation. When a write is in progress, poll the BUSY bit before sending any new commands to assure that the new commands are properly received by the device.

To read the STATUS or Configuration registers, the host drives CE# low, then sends the Read Status Register command cycle (05H) or the Read Configuration Register command (35H). A dummy cycle is required in SQI mode. Immediately after the command cycle, the device outputs data on the falling edge of the SCK signal. The data output stream continues until terminated by a low-to-high transition on CE#. See Figures 5-28 and 5-29 for the instruction sequence.

FIGURE 5-28: READ STATUS REGISTER AND READ CONFIGURATION REGISTER SEQUENCE (SQI)

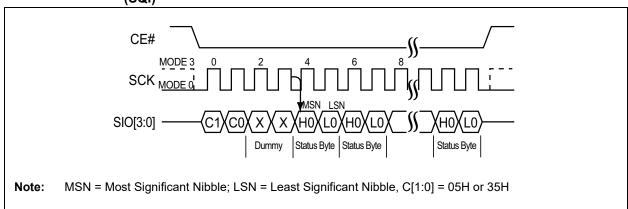
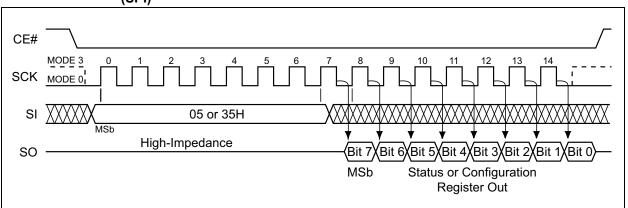


FIGURE 5-29: READ STATUS REGISTER AND READ CONFIGURATION REGISTER SEQUENCE (SPI)



5.30 Write Status Register (WRSR)

The Write Status Register (WRSR) command writes new values to the Configuration register. To execute a Write Status Register operation, the host drives CE# low, then sends the Write Status Register command cycle (01H), two cycles of data and then drives CE# high. Values in the second data cycle will be accepted by the device (see Figures 5-30 and 5-31).

FIGURE 5-30: WRITE STATUS REGISTER SEQUENCE (SQI)

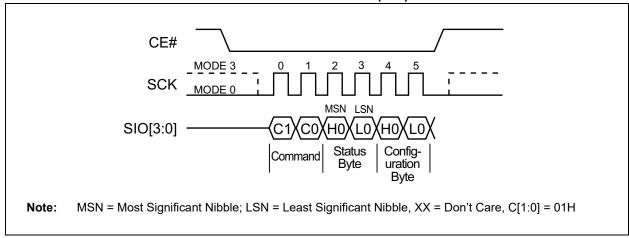
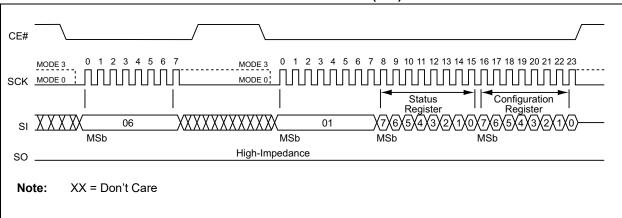


FIGURE 5-31: WRITE STATUS REGISTER SEQUENCE (SPI)



5.31 Write Enable (WREN)

The Write Enable (WREN) instruction sets the Write Enable Latch bit in the STATUS register to '1,' allowing write operations to occur. The WREN instruction must be executed prior to any of the following operations: Sector Erase, Block Erase, Chip Erase, Page Program, Program Security ID, Lockout Security ID, Write Block Protection Register, Lock-Down Block Protection Register, Nonvolatile Write Lock Lock-Down Register, SPI Quad Page program and Write Status Register. To execute a Write Enable, the host drives CE# low, then sends the Write Enable command cycle (06H) and drives CE# high. See Figures 5-32 and 5-33 for the WREN instruction sequence.



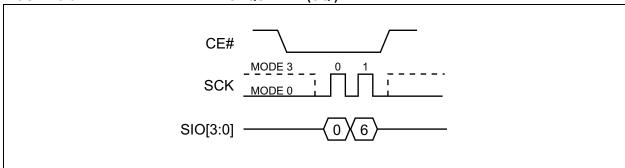
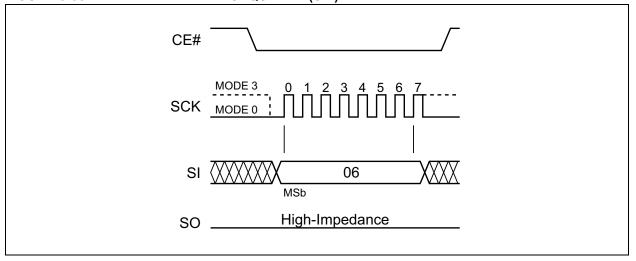


FIGURE 5-33: WRITE ENABLE SEQUENCE (SPI)

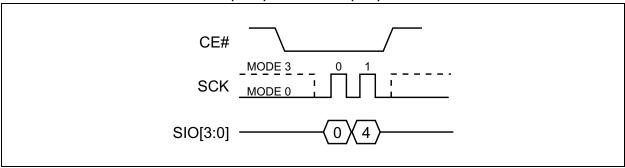


5.32 Write Disable (WRDI)

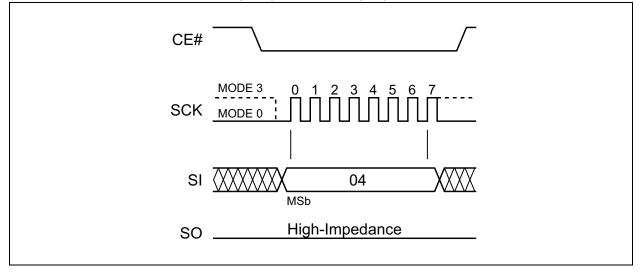
The Write Disable (WRDI) instruction sets the Write Enable Latch bit in the STATUS register to '0,' preventing write operations. The WRDI instruction is ignored during any internal write operations. Any write operation started before executing WRDI will complete. Drive CE# high before executing WRDI.

To execute a Write Disable, the host drives CE# low, sends the Write Disable command cycle (04H), then drives CE# high (see Figures 5-34 and 5-35).

FIGURE 5-34: WRITE DISABLE (WRDI) SEQUENCE (SQI)







5.33 Read Block Protection Register (RBPR)

The Read Block Protection Register instruction outputs the Block Protection register data which determines the protection status. To execute a Read Block Protection Register operation, the host drives CE# low and then sends the Read Block Protection Register command cycle (72H). A dummy cycle is required in SQI mode.

After the command cycle, the device outputs data on the falling edge of the SCK signal starting with the Most Significant bit(s); see Table 5-6 for definitions of each bit in the Block Protection register. The RBPR command does not wrap around. After all data have been output, the device will output 0H until terminated by a low-to-high transition on CE# (see Figures 5-36 and 5-37).

FIGURE 5-36: READ BLOCK PROTECTION REGISTER SEQUENCE (SQI)

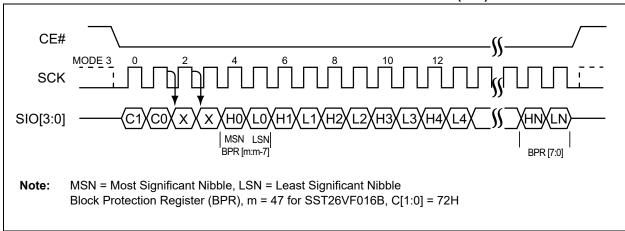
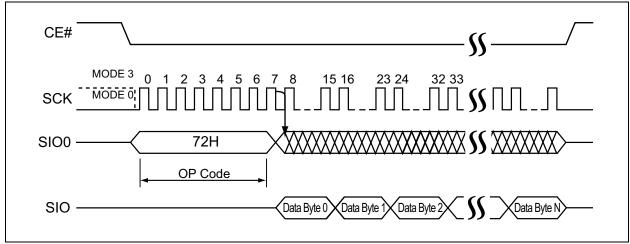


FIGURE 5-37: READ BLOCK PROTECTION REGISTER SEQUENCE (SPI)



5.34 Write Block Protection Register (WBPR)

The Write Block Protection Register (WBPR) command changes the Block Protection register data to indicate the protection status. Execute WREN before executing WBPR.

To execute a Write Block Protection Register operation, the host drives CE# low, sends the Write Block Protection Register command cycle (42H), sends 18 cycles of data and finally drives CE# high. Data input must be Most Significant bit(s) first. See Table 5-6 for definitions of each bit in the Block Protection register (see Figures 5-38 and 5-39).

FIGURE 5-38: WRITE BLOCK PROTECTION REGISTER SEQUENCE (SQI)

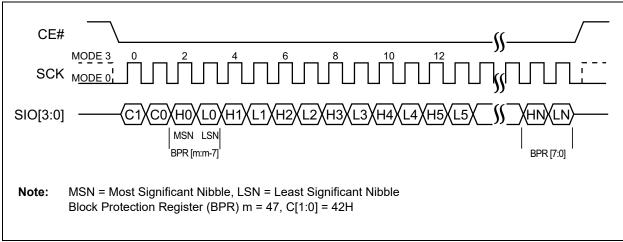
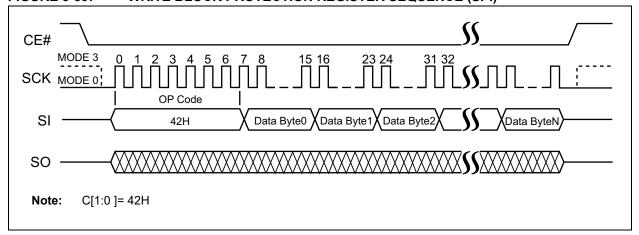


FIGURE 5-39: WRITE BLOCK PROTECTION REGISTER SEQUENCE (SPI)

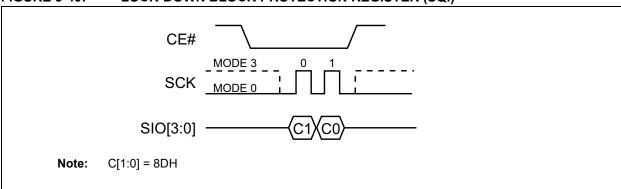


5.35 Lock-Down Block Protection Register (LBPR)

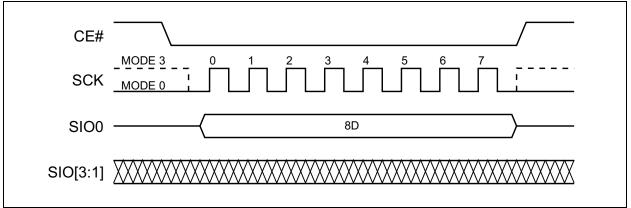
The Lock-Down Block Protection Register instruction prevents changes to the Block Protection register during device operation. Lock-Down resets after power cycling; this allows the Block Protection register to be changed. Execute WREN before initiating the Lock-Down Block Protection Register instruction.

To execute a Lock-Down Block Protection Register, the host drives CE# low, then sends the Lock-Down Block Protection Register command cycle (8DH), then drives CE# high.

FIGURE 5-40: LOCK-DOWN BLOCK PROTECTION REGISTER (SQI)







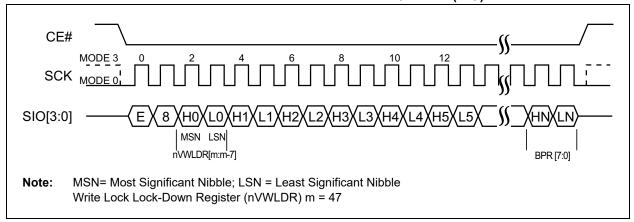
5.36 Nonvolatile Write Lock Lock-Down Register (nvwldr)

The Nonvolatile Write Lock Lock-Down Register (nVWLDR) instruction controls the ability to change the Write Lock bits in the Block Protection register. Execute WREN before initiating the nVWLDR instruction.

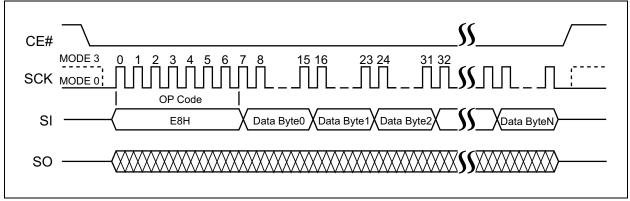
To execute nVWLDR, the host drives CE# low, then sends the nVWLDR command cycle (E8H), followed by 18 cycles of data, and then drives CE# high.

After CE# goes high, the nonvolatile bits are programmed and the programming time-out must complete before any additional commands, other than Read Status Register, can be entered. Poll the BUSY bit in the STATUS register, or wait TPP, for the completion of the internal, self-timed, Write operation. Data inputs must be Most Significant bit(s) first.

FIGURE 5-42: WRITE LOCK LOCK-DOWN REGISTER SEQUENCE (SQI)





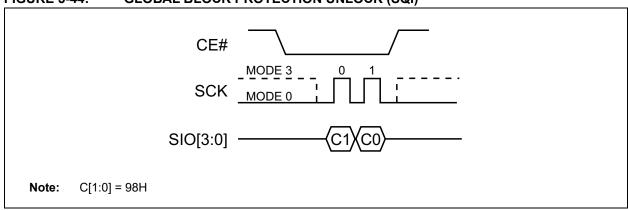


5.37 Global Block Protection Unlock (ULBPR)

The Global Block Protection Unlock (ULBPR) instruction clears all write protection bits in the Block Protection register, except for those bits that have been locked down with the ${\tt nVWLDR}$ command. Execute WREN before initiating the ULBPR instruction.

To execute a <code>ULBPR</code> instruction, the host drives CE# low, then sends the <code>ULBPR</code> command cycle (98H) and then drives CE# high.

FIGURE 5-44: GLOBAL BLOCK PROTECTION UNLOCK (SQI)





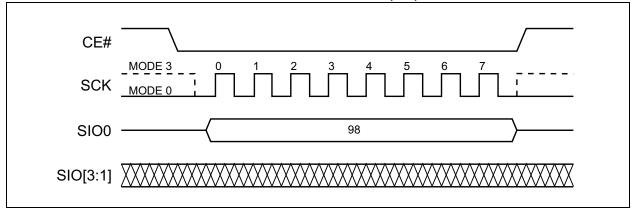


TABLE 5-6: BLOCK PROTECTION REGISTER FOR SST26VF016B⁽¹⁾

B	BPR Bits	Address Range	Protected Bloc
Read Lock	Write Lock/nVWLDR ⁽²⁾	Addiess Runge	1 Totocted Bloc
47	46	1FE000H-1FFFFFH	8 Kbytes
45	44	1FC000H-1FDFFFH	8 Kbytes
43	42	1FA000H-1FBFFFH	8 Kbytes
41	40	1F8000H-1F9FFFH	8 Kbytes
39	38	006000H-007FFFH	8 Kbytes
37	36	004000H-005FFFH	8 Kbytes
35	34	002000H-003FFFH	8 Kbytes
33	32	000000H-001FFFH	8 Kbytes
	31	1F0000H-1F7FFFH	32 Kbytes
	30	008000H-00FFFFH	32 Kbytes
	29	1E0000H-1EFFFFH	64 Kbytes
	28	1D0000H-1DFFFFH	64 Kbytes
	27	1C0000H-1CFFFFH	64 Kbytes
	26	1B0000H-1BFFFFH	64 Kbytes
	25	1A0000H-1AFFFFH	64 Kbytes
	24	190000H-19FFFFH	64 Kbytes
	23	180000H-18FFFFH	64 Kbytes
	22	170000H-17FFFFH	64 Kbytes
	21	160000H-16FFFFH	64 Kbytes
	20	150000H-15FFFFH	64 Kbytes
	19	140000H-14FFFFH	64 Kbytes
	18	130000H-13FFFFH	64 Kbytes
	17	120000H-12FFFFH	64 Kbytes
	16	110000H-11FFFFH	64 Kbytes
	15	100000H-10FFFFH	64 Kbytes
	14	0F0000H-0FFFFFH	64 Kbytes
	13	0E0000H-0EFFFFH	64 Kbytes
	12	0D0000H-0DFFFFH	64 Kbytes
	11	0C0000H-0CFFFFH	64 Kbytes
	10	0B0000H-0BFFFFH	64 Kbytes
	9	0A0000H-0AFFFFH	64 Kbytes
	8	090000H-09FFFFH	64 Kbytes
	7	080000H-08FFFFH	64 Kbytes
	6	070000H-07FFFFH	64 Kbytes
	5	060000H-06FFFFH	64 Kbytes
	4	050000H-05FFFFH	64 Kbytes
	3	040000H-04FFFFH	64 Kbytes
	2	030000H-03FFFFH	64 Kbytes
	1	020000H-02FFFFH	64 Kbytes
	0	010000H-01FFFFH	64 Kbytes

Note 1: The default state after a Power-on Reset is write-protected BPR[47:0] = 5555 FFFF FFFF.

^{2:} nVWLDR bits are One-Time-Programmable. Once a WLLDR bit is set, the protection state of that particular block is permanently write-locked.

5.38 **Deep Power-Down**

The Deep Power-Down (DPD) instruction puts the device in the lowest power consumption mode - the Deep Power-Down mode. The Deep Power-Down instruction is ignored during an internal write operation. While the device is in Deep Power-Down mode, all instructions will be ignored except for the Release Deep Power-Down instruction.

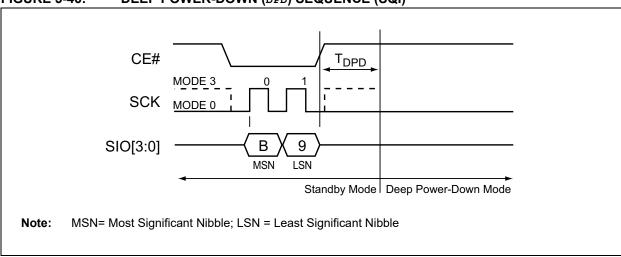
Enter Deep Power-Down mode by initiating the Deep Power-Down (DPD) instruction (B9H) while driving CE# low. CE# must be driven high before executing the DPD instruction. After CE# is driven high, it requires a delay of TDPD before the standby current ISB is reduced to deep power-down current IDPD. See Table 5-7 for Deep Power-Down timing. If the device is busy performing an internal erase or program operation, initiating a Deep Power-Down instruction will not place the device in Deep Power-Down mode. See Figures 5-47 and for the DPD instruction sequence.

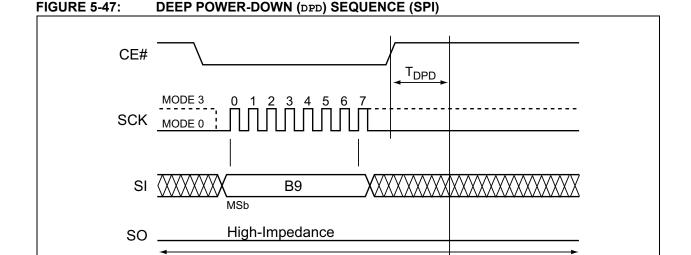
TABLE 5-7: DEEP POWER-DOWN

FIGURE 5-47:

Symbol	Parameter	Min.	Max.	Units
TDPD	CE# High to Deep Power-Down		3	μs
TSBR	CE# High to Standby Mode		10	μs







Standby Mode | Deep Power-Down Mode

5.39 Release from Deep Power-Down and Read ID

Release from Deep Power-Down (RDPD) and Read ID instruction exits Deep Power-Down mode. To exit Deep Power-Down mode, execute the RDPD. During this command, the host drives CE# low, then sends the Deep Power-Down command cycle (ABH) and then drives CE# high. The device will return to Standby mode and be ready for the next instruction after TSBR.

To execute RDPD and read the Device ID, the host drives CE# low, then sends the Deep Power-Down command cycle (ABH), three dummy clock cycles and then drives CE# high. The device outputs the Device ID on the falling edge of the SCK signal following the dummy cycles. The data output stream is continuous until terminated by a low-to-high transition on CE and will return to Standby mode and be ready for the next instruction after TSBR. See Figures 5-48 and 5-49 for the command sequence.

FIGURE 5-48: RELEASE FROM DEEP POWER-DOWN (RDPD) AND READ ID SEQUENCE (SQI)

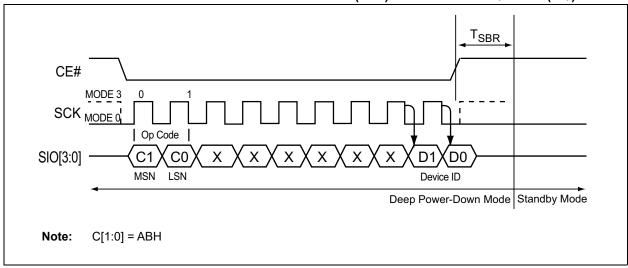
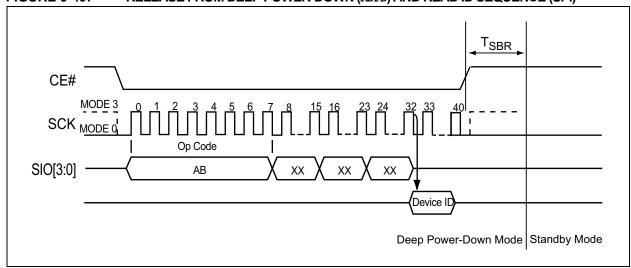


FIGURE 5-49: RELEASE FROM DEEP POWER-DOWN (RDPD) AND READ ID SEQUENCE (SPI)



6.0 ELECTRICAL SPECIFICATIONS

Absolute Maximum Ratings (†)

Temperature under bias	55°C to +125°C
Storage temperature	65°C to +150°C
DC voltage on any pin to ground potential	0.5V to VDD+0.5V
Transient voltage (<20 ns) on any pin to ground potential	2.0V to VDD+2.0V
Package power dissipation capability (TA = +25°C)	1.0W
Surface mount solder reflow temperature	+260°C for 10 seconds
Output short circuit current ⁽¹⁾	50 mA

† NOTICE: Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at those or any other conditions above those indicated in the operational listings of this specification is not implied. Exposure to maximum rating conditions for extended periods may affect device reliability.

Note 1: Output shorted for no more than one second. No more than one output shorted at a time.

TABLE 6-1: OPERATING RANGE

Range	Ambient Temperature	VDD
Industrial	-40°C to +85°C	2.3V-3.6V
Industrial Plus	-40°C to +105°C	2.3V-3.6V
Extended ⁽¹⁾	-40°C to +125°C	2.3V-3.6V

Note 1: Maximum operating frequency for Extended temperature is 80 MHz.

TABLE 6-2: AC CONDITIONS OF TEST⁽¹⁾

Input Rise/Fall Time	Output Load
3 ns	CL = 30 pF

Note 1: See Figure 8-5.

6.1 Power-Up Specifications

All functionalities and DC specifications are specified for a VDD ramp rate of greater than 1V per 100 ms (0V to 3.0V in less than 300 ms). See Table 6-3 and Figure 6-1 for more information.

When VDD drops from the operating voltage to below the minimum VDD threshold at power-down, all operations are disabled and the device does not respond to commands. Data corruption may result if a power-down occurs while a write registers, program or erase operation is in progress (see Figure 6-2).

TABLE 6-3: RECOMMENDED SYSTEM POWER-UP/DOWN TIMINGS

Symbol	Parameter	Minimum	Maximum	Units	Conditions
TPU-READ ⁽¹⁾	VDD Min to Read Operation	100	_	μs	
TPU-WRITE ⁽¹⁾	VDD Min to Write Operation	100	_	μs	
TPD ⁽¹⁾	Power-Down Duration	100	_	ms	
Voff	VDD Off Time	_	0.3	V	0V recommended

Note 1: This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

FIGURE 6-1: POWER-UP TIMING DIAGRAM

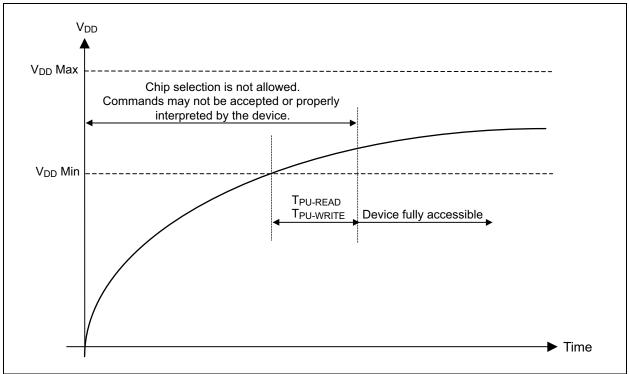
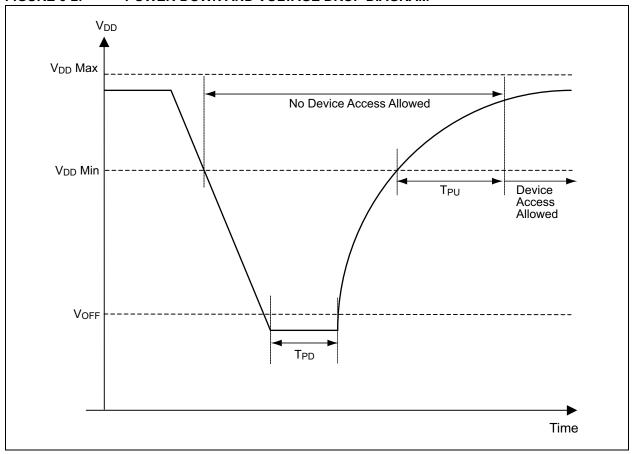


FIGURE 6-2: POWER-DOWN AND VOLTAGE DROP DIAGRAM



7.0 DC CHARACTERISTICS

TABLE 7-1: DC OPERATING CHARACTERISTICS (VDD = 2.3V-3.6V)

Cumhal	Davamatav	Limits				Took Conditions
Symbol	Parameter	Min.	Тур.	Max.	Units	Test Conditions
IDDR	Read Current	_	1	20	mA	VDD = VDD maximum, CE# = 0.1 VDD/0.9 VDD@80 MHz, SO = open
IDDR1	Read Current	_	8	15	mA	VDD = VDD maximum, CE# = 0.1 VDD/0.9 VDD@40 MHz, SO = open
IDDR2	Read Current	_		20	mA	VDD = VDD maximum, CE# = 0.1 VDD/0.9 VDD@104 MHz, SO = open
IDDW	Program and Erase Current	_	_	25	mA	V _{DD} maximum
ISB1	Standby Current	_	15	45	μA	CE# = VDD, VIN = VDD or Vss @+105°C
ISB2	Standby Current	_	_	80	μA	CE# = VDD, VIN = VDD or Vss @+125°C
IDPD	Deep Power-Down Current	_	8	25	μA	CE# = VDD, VIN = VDD or Vss
ILI	Input Leakage Current	_	_	2	μA	VIN = GND to VDD, VDD = VDD maximum
ILO	Output Leakage Current	_	_	2	μA	VOUT = GND to VDD, VDD = VDD maximum
VIL	Input Low Voltage		_	0.8	V	VDD = VDD minimum
VIH	Input High Voltage	0.7 VDD	_	_	V	VDD = VDD maximum
Vol	Output Low Voltage	_	_	0.2	V	IOL = 100 μA, VDD = VDD minimum
Vон	Output High Voltage	VDD-0.2	_	_	V	IOH = -100 μA, VDD = VDD minimum

TABLE 7-2: CAPACITANCE (TA = +25°C, F = 1 MHZ, OTHER PINS OPEN)

Parameter	Description	Test Condition	Maximum
Cout ⁽¹⁾	Output Pin Capacitance	Vout = 0V	8 pF
CIN ⁽¹⁾	Input Capacitance	VIN = 0V	6 pF

Note 1: This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

TABLE 7-3: RELIABILITY CHARACTERISTICS

Symbol	Parameter	Minimum Specification	Unit	Test Method
NEND ⁽¹⁾	Endurance	100,000	Cycles	JEDEC [®] Standard A117
TDR ⁽¹⁾	Data Retention	100	Years	JEDEC [®] Standard A103
ILTH ⁽¹⁾	Latch Up	100 + IDD	mA	JEDEC [®] Standard A78

Note 1: This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

TABLE 7-4: WRITE TIMING PARAMETERS (VDD = 2.3V-3.6V)

Symbol	Parameter	Minimum	Maximum	Units
TSE	Sector Erase	_	25	ms
Тве	Block Erase	_	25	ms
TSCE	Chip Erase	_	50	ms
TPP ⁽¹⁾	Page Program	_	1.5	ms
TPSID	Program Security ID	_	1.5	ms
Tws	Write Suspend Latency	_	25	μs
TWPEN	Write Protection Enable Bit Latency	_	25	ms

Note 1: Estimate for typical conditions less than 256 bytes: Programming Time (μ s) = 55 + (3.75 x # of bytes)

8.0 AC CHARACTERISTICS

TABLE 8-1: AC OPERATING CHARACTERISTICS (VDD = 2.3V-3.6V)⁽¹⁾

0	Parameter	Limits	Limits - 40 MHz		Limits - 80 MHz ⁽²⁾		Limits - 104 MHz	
Symbol		Min	Max	Min	Max	Min	Max	Units
FCLK	Serial Clock Frequency	_	40	_	80		104	MHz
TCLK	Serial Clock Period	_	25	_	12.5	_	9.6	ns
Тѕскн	Serial Clock High Time	11	_	5.5	_	4.5	_	ns
TSCKL	Serial Clock Low Time	11	_	5.5	_	4.5	_	ns
TSCKR ⁽³⁾	Serial Clock Rise Time (slew rate)	0.1	_	0.1	_	0.1	_	V/ns
TSCKF ⁽³⁾	Serial Clock Fall Time (slew rate)	0.1	_	0.1	_	0.1	_	V/ns
TCES ⁽⁴⁾	CE# Active Setup Time	8	_	5	_	5	_	ns
TCEH ⁽⁴⁾	CE# Active Hold Time	8	_	5	_	5	_	ns
Tchs ⁽⁴⁾	CE# Not Active Setup Time	8	_	5	_	5	_	ns
Тснн ⁽⁴⁾	CE# Not Active Hold Time	8	_	5	_	5	_	ns
Тсрн	CE# High Time	25	_	12.5	_	12	_	ns
Тснz	CE# High to High-Z Output	_	19	_	12.5		12	ns
Tclz	SCK Low to Low-Z Output	0	_	0	_	0	_	ns
THLS	HOLD# Low Setup Time	8	_	5	_	5	_	ns
THHS	HOLD# High Setup Time	8	_	5	_	5	_	ns
THLH	HOLD# Low Hold Time	8	_	5	_	5	_	ns
Тннн	HOLD# High Hold Time	8	_	5	_	5	_	ns
THZ	HOLD# Low-to-High-Z Output	_	8	_	8	_	8	ns
TLZ	HOLD# High-to-Low-Z Output		8		8		8	ns
TDS	Data In Setup Time	3	_	3	_	3	_	ns
TDH	Data In Hold Time	4		4	_	4	_	ns
Тон	Output Hold from SCK Change	0		0	_	0		ns
Tv	Output Valid from SCK		8/5 ⁽⁵⁾	_	8/5 ⁽⁵⁾	_	8/5 ⁽⁵⁾	ns

Note 1: Maximum operating frequency for 2.7V-3.6V is 104 MHz and for 2.3V-3.6V is 80 MHz.

^{2:} Maximum frequency for +125°C is 80 MHz.

^{3:} Maximum Rise and Fall time may be limited by TSCKH and TSCKL requirements.

^{4:} Relative to SCK.

⁵: 30 pF/10 pF

FIGURE 8-1: HOLD TIMING DIAGRAM

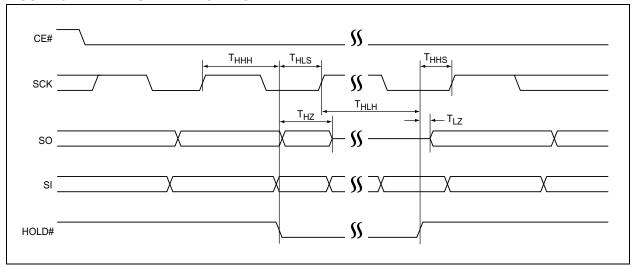


FIGURE 8-2: SERIAL INPUT TIMING DIAGRAM

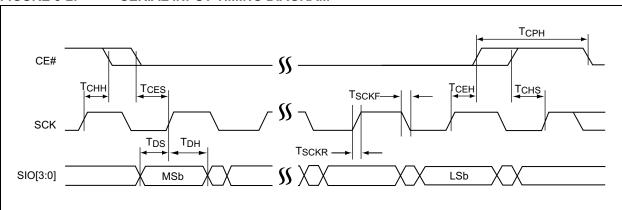


FIGURE 8-3: SERIAL OUTPUT TIMING DIAGRAM

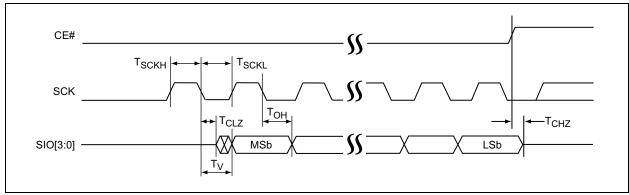


TABLE 8-2: RESET TIMING PARAMETERS

T _{R(i)}	Parameter	Minimum	Maximum	Units
Tr(o)	Reset to Read (non-data operation)	_	20	ns
TR(P)	Reset Recovery from Program or Suspend	_	100	μs
TR(E)	Reset Recovery from Erase	_	1	ms

FIGURE 8-4: RESET TIMING DIAGRAM

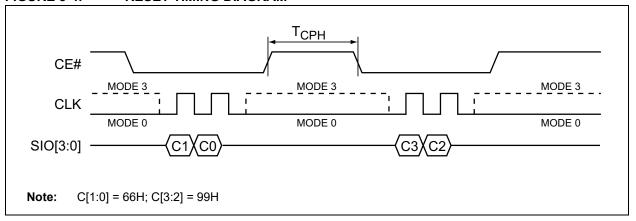
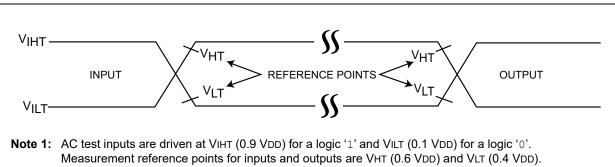


FIGURE 8-5: AC INPUT/OUTPUT REFERENCE WAVEFORMS

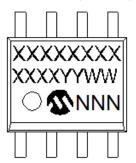


- Input rise and fall times (10% \leftrightarrow 90%) are <3 ns.
 - 2: VHT = VHIGH Test
 - VLT = VLOW Test
 - VIHT = VINPUT HIGH Test
 - VILT = VINPUT LOW Test

9.0 PACKAGING INFORMATION

9.1 Package Marking

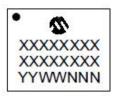
8-Lead SOIC (3.90 mm)

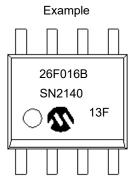


8-Lead SOIJ (5.28 mm



8-Lead WDFN (5x6 mm)





Example



Example



Part Number	1 st Line Marking Codes			
Part Number	SOIC	SOIJ	WDFN	
SST26VF016B	26F016B	26F016B	26F016B	

Legend: XX...X Part number or part number code

Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')

NNN Alphanumeric traceability code (2 characters for small packages)

RoHS compliant JEDEC® designator for Matte Tin (Sn)

Note: For very small packages with no room for the RoHS compliant JEDEC[®] designator (e3), the marking will only appear on the outer carton or reel label.

es, the marking will only appear on the outer carton of reer laber.

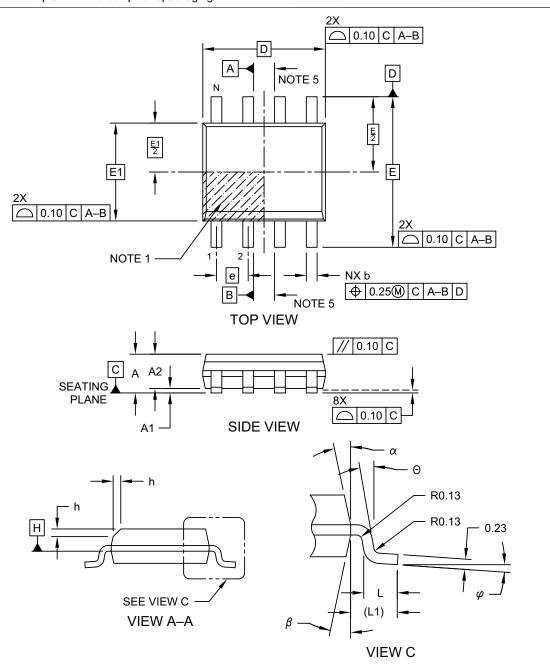
In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

Note:

9.2 Packaging Diagrams

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm (.150 ln.) Body [SOIC]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

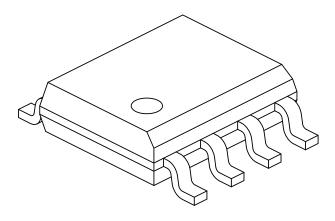


Microchip Technology Drawing No. C04-057-SN Rev F Sheet 1 of 2

Note:

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm (.150 ln.) Body [SOIC]

For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	MILLIMETERS				
Dimension	MIN	NOM	MAX		
Number of Pins	Ν		8		
Pitch	е		1.27 BSC		
Overall Height	Α	-	ı	1.75	
Molded Package Thickness	A2	1.25	ı	-	
Standoff §	A1	0.10	ı	0.25	
Overall Width	Е	6.00 BSC			
Molded Package Width	E1	3.90 BSC			
Overall Length	D	4.90 BSC			
Chamfer (Optional)	h	0.25	1	0.50	
Foot Length	L	0.40	ı	1.27	
Footprint	L1	1.04 REF			
Foot Angle	φ	0°	ı	8°	
Lead Thickness	С	0.17	1	0.25	
Lead Width	b	0.31	ı	0.51	
Mold Draft Angle Top	α	5°	-	15°	
Mold Draft Angle Bottom	β	5°	-	15°	

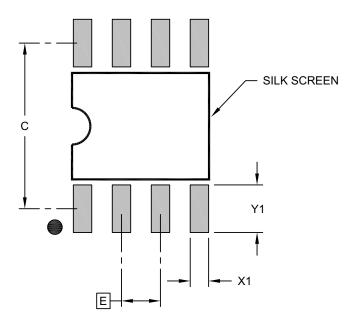
Notes

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. § Significant Characteristic
- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.15mm per side.
- 4. Dimensioning and tolerancing per ASME Y14.5M $\,$
 - BSC: Basic Dimension. Theoretically exact value shown without tolerances.
 - REF: Reference Dimension, usually without tolerance, for information purposes only.
- 5. Datums A & B to be determined at Datum H.

Microchip Technology Drawing No. C04-057-SN Rev F Sheet 2 of 2

8-Lead Plastic Small Outline (SN) - Narrow, 3.90 mm (.150 ln.) Body [SOIC]

For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	N	IILLIMETER	S	
Dimension	MIN	NOM	MAX	
Contact Pitch	Е		1.27 BSC	
Contact Pad Spacing	C		5.40	
Contact Pad Width (X8)	X1			0.60
Contact Pad Length (X8)			1.55	

Notes:

Note:

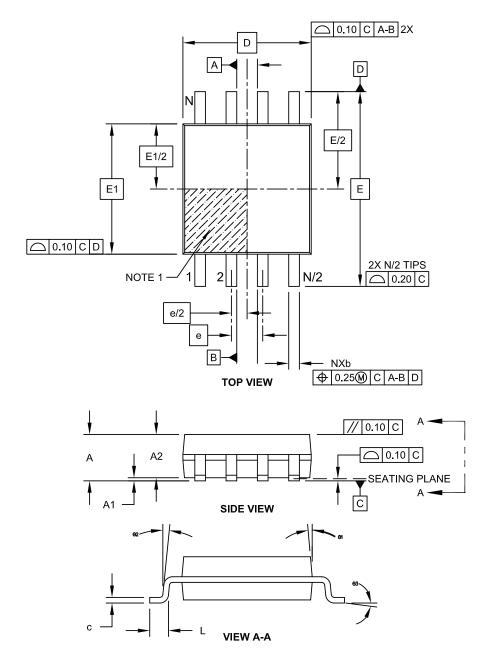
1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-2057-SN Rev F

8-Lead Plastic Small Outline (SM) - Medium, 5.28 mm Body [SOIJ]

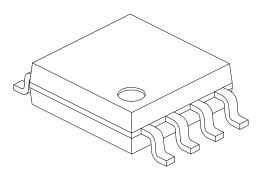
Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



Microchip Technology Drawing C04-056C Sheet 1 of 2

8-Lead Plastic Small Outline (SM) - Medium, 5.28 mm Body [SOIJ]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	N	ILLIMETER	S		
Dimension	Dimension Limits				
Number of Pins	N		8		
Pitch	е		1.27 BSC		
Overall Height	Α	1.77	ı	2.03	
Standoff §	A1	0.05		0.25	
Molded Package Thickness	A2	1.75	-	1.98	
Overall Width	E	7.94 BSC			
Molded Package Width	E1	5,25 BSC			
Overall Length	D	5.26 BSC			
Foot Length	L	0.51	ı	0.76	
Lead Thickness	С	0.15	-	0.25	
Lead Width	b	0.36	-	0.51	
Mold Draft Angle	Θ1	-	-	15°	
Lead Angle	Θ2	0°	-	8°	
Foot Angle	Θ3	0°	-	8°	

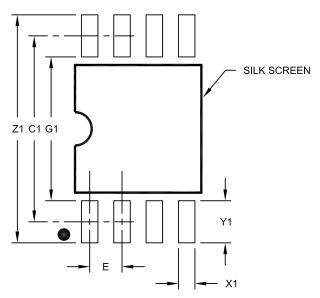
Notes:

- 1. SOIJ, JEITA/EIAJ Standard, Formerly called SOIC
- 2. § Significant Characteristic
- 3. Dimensions D and E1 do not include mold flash or protrusions. Mold flash or protrusions shall not exceed 0.25mm per side.

Microchip Technology Drawing No. C04-056C Sheet 2 of 2

8-Lead Plastic Small Outline (SM) - Medium, 5.28 mm Body [SOIJ]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	MILLIMETERS			
Dimension	Limits	MIN	NOM	MAX
Contact Pitch	Contact Pitch E			
Overall Width	Z1			9.00
Contact Pad Spacing	C1		7.30	
Contact Pad Width (X8)	X1			0.65
Contact Pad Length (X8)	Y1			1.70
Distance Between Pads	G1	5.60		
Distance Between Pads	G	0.62		

Notes:

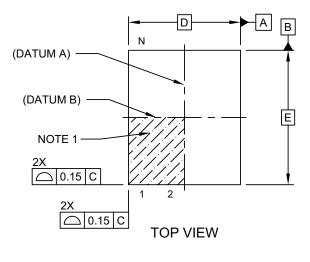
1. Dimensioning and tolerancing per ASME Y14.5M

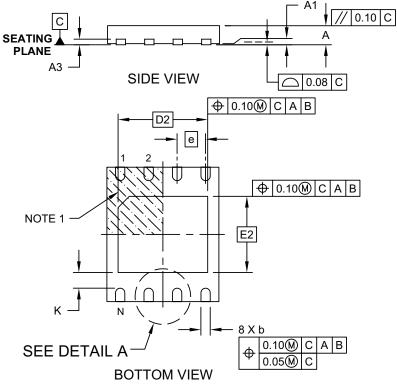
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing No. C04-2056C

8-Lead Plastic Very, Very Thin Small Outline No-Lead (MF) - 5x6 mm Body [WDFN]

Note: For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging

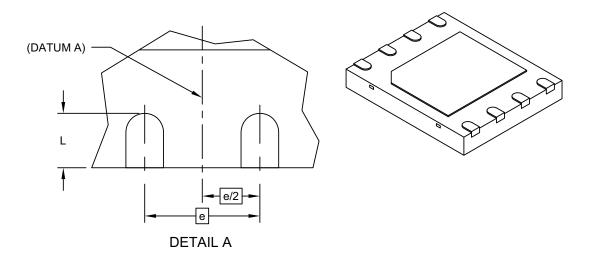




Microchip Technology Drawing C04-210B Sheet 1 of 2

8-Lead Plastic Very, Very Thin Small Outline No-Lead (MF) - 5x6 mm Body [WDFN]

For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



	l. N	IILLIMETER:	S		
Dimensior	Dimension Limits				
Number of Terminals	N		8		
Pitch	е		1.27 BSC		
Overall Height	Α	0.70	0.75	0.80	
Standoff	A1	0.00	0.02	0.05	
Terminal Thickness	A3		0.20 REF		
Overall Width	D		5.00 BSC		
Exposed Pad Width	D2	4.00 BSC			
Overall Length	Е		6.00 BSC		
Exposed Pad Length	E2		3.40 BSC		
Terminal Width	b	0.35	0.42	0.48	
Terminal Length	L	0.50	0.60	0.70	
Terminal-to-Exposed-Pad	K	0.20	-	-	

Notes:

- 1. Pin 1 visual index feature may vary, but must be located within the hatched area.
- 2. Package is saw singulated
- 3. Dimensioning and tolerancing per ASME Y14.5M $\,$

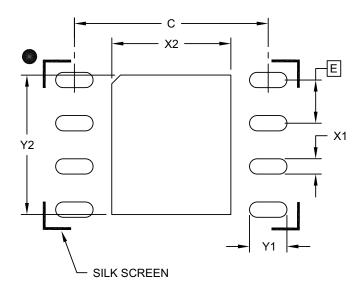
BSC: Basic Dimension. Theoretically exact value shown without tolerances.

REF: Reference Dimension, usually without tolerance, for information purposes only.

Microchip Technology Drawing C04-210B Sheet 2 of 2

8-Lead Plastic Very, Very Thin Small Outline No-Lead (MF) - 5x6 mm Body [WDFN]

For the most current package drawings, please see the Microchip Packaging Specification located at http://www.microchip.com/packaging



RECOMMENDED LAND PATTERN

	N	IILLIMETER:	S	
Dimension	Limits	MIN	NOM	MAX
Contact Pitch	Contact Pitch E			
Optional Center Pad Width	X2			3.50
Optional Center Pad Length	Y2			4.10
Contact Pad Spacing	С		5.70	
Contact Pad Width (X8)	X1			0.45
Contact Pad Length (X8)	Y1			1.10

Notes:

Note:

1. Dimensioning and tolerancing per ASME Y14.5M

BSC: Basic Dimension. Theoretically exact value shown without tolerances.

Microchip Technology Drawing C04-2210A

10.0 REVISION HISTORY

Revision G (January 2022)

Added Product Identification System section for Automotive; Updated SOIC package drawings; Reformatted some sections for better readability.

Revision F (May 2019)

Added IDDR to Table 7-1; Corrected SDIOR maximum frequency value in Table 5-1.

Revision E (November 2018)

Added extended temperature references throughout.

Revision D (December 2017)

Corrected High-Speed Clock Frequency range; Corrected Table 6-1; Added Automotive AEC-Q100 information.

Revision C (August 2015)

Extended the voltage range; Added extended temperature range.

Revision B (February 2015)

Removed the SST26VF016BA device from the data sheet; Added Part Markings.

Revision A (May 2014)

Initial release of this document.

THE MICROCHIP WEBSITE

Microchip provides online support via our website at www.microchip.com. This website is used as a means to make files and information easily available to customers. Accessible by using your favorite Internet browser, the website contains the following information:

- Product Support Data sheets and errata, application notes and sample programs, design resources, user's guides and hardware support documents, latest software releases and archived software
- General Technical Support Frequently Asked Questions (FAQ), technical support requests, online discussion groups, Microchip consultant program member listing
- Business of Microchip Product selector and ordering guides, latest Microchip press releases, listing of seminars and events, listings of Microchip sales offices, distributors and factory representatives

CUSTOMER CHANGE NOTIFICATION SERVICE

Microchip's customer notification service helps keep customers current on Microchip products. Subscribers will receive e-mail notification whenever there are changes, updates, revisions or errata related to a specified product family or development tool of interest.

To register, access the Microchip website at www.microchip.com. Under "Support", click on "Customer Change Notification" and follow the registration instructions.

CUSTOMER SUPPORT

Users of Microchip products can receive assistance through several channels:

- · Distributor or Representative
- · Local Sales Office
- · Field Application Engineer (FAE)
- · Technical Support

Customers should contact their distributor, representative or Field Application Engineer (FAE) for support. Local sales offices are also available to help customers. A listing of sales offices and locations is included in the back of this document.

Technical support is available through the website at: http://microchip.com/support

PRODUCT IDENTIFICATION SYSTEM (NON-AUTOMOTIVE)

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO.	X (1)	- <u>xxx</u>	X T	/xx	Valid Combinations:
Device -	Tape an Optio		Operating Frequency	Temperature Range	Package	SST26VF016B-104I/SM SST26VF016BT-104I/SM SST26VF016B-104I/SN
Device:	SST26	6VF016B		2.5V/3.0V, SQI Flash I# Pin Enable at Pow		SST26VF016BT-104I/SN SST26VF016B-104I/MF SST26VF016BT-104I/MF
Tape and Rec Option:	el Blank T	= =	Standard Tape and	packaging (tube) Reel ⁽¹⁾		SST26VF016B-104V/SM SST26VF016BT-104V/SM
Operating Frequency:	104 80	= =	104 MHz 80 MHz			SST26VF016B-104V/SN SST26VF016BT-104V/SN SST26VF016B-104V/MF
Temperature Range:	I V E	=	-40°C to+	-85°C (Industrial) -105°C (Industrial Pl -125°C (Extended)	lus)	SST26VF016BT-104V/MF SST26VF016B-80E/SM SST26VF016BT-80E/SM
Package:	SN	=	(.150 ln) l	mall Outline - Narrov Body, 8-Lead (SOIC	;) [^]	SST26VF016B-80E/SN SST26VF016BT-80E/SN
	SM MF	=	Body, 8-L Plastic Ve	mall Outline - Mediu ead (SOIJ) ery, Very Thin Small – 5x6 mm Body, 8-L	Outline	SST26VF016B-80E/MF SST26VF016BT-80E/MF Note 1: Tape and Reel identifier only appears in the
						catalog part number description. This identifier is used for ordering purposes and is not printed on the device package. Check with your Microchip Sales Office for package availability with the Tape and Reel option.

PRODUCT IDENTIFICATION SYSTEM (AUTOMOTIVE)

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

ART NO.	<u>X</u> ⁽¹⁾	– <u>xx</u>	<u>x</u>	X	<u>/XX</u>	XXX (
Device Tape a	l ind Reel Option	Operat Freque		mperature Range	Package	Variant
Device:	SST26VI	=016B =		t, 2.5V/3.0V, 9 lold# Pin Enal		
Tape and Reel Option:	Blank T	= =		ırd packaginç nd ¹ Reel	g (tube)	
Operating Frequency:	104 80	= =	104 MI 80 MH			
Temperature Range:	I V E	= = =	-40°C	to+85°C (AE0 to+105°C (AE0 to+125°C (AE	EC-Q100 Gra	ade 3)
Package:	SN	=		Small Outlin n) Body, 8-Le		3.90 mm
	SM	=		Small Outlin 3-Lead (SOIJ		5.28 mm
	MF	=	Plastic No-Lea	Very, Very T ad – 5x6 mm	hin Small Ou Body, 8-Lead	tline d (WDFN)
Variant:(2,3)	70SVAO 70SVXX			ard Automotiv ner-Specific A		

Valid Combinations:

SST26VF016B-80E/SN70SVAO SST26VF016B-80E/SM70SVAO SST26VF016B-80E/MF70SVAO SST26VF016BT-80E/SN70SVAO SST26VF016BT-80E/SM70SVAO SST26VF016BT-80E/MF70SVAO

SST26VF016B-104V/SN70SVAO SST26VF016B-104V/SM70SVAO SST26VF016B-104V/MF70SVAO SST26VF016BT-104V/SN70SVAO SST26VF016BT-104V/SM70SVAO SST26VF016BT-104V/MF70SVAO

SST26VF016B-104I/SN70SVAO SST26VF016B-104I/SM70SVAO SST26VF016B-104I/MF70SVAO SST26VF016BT-104I/SN70SVAO SST26VF016BT-104I/SM70SVAO SST26VF016BT-104I/MF70SVAO

- Note 1: Tape and Reel identifier only appears in the catalog part number description. This identifier is used for ordering purposes and is not printed on the device package. Check with your Microchip Sales Office for package availability with the Tape and Reel option.
 - The VAO/VXX automotive variants have been designed, manufactured, tested and qualified in accordance with AEC-Q100 requirements for automotive applications.
 - For customers requesting a PPAP, a customer-specific part number will be generated and provided. A PPAP is not provided for VAO part numbers.

11.0 APPENDIX

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (1 OF 17)

IABLE II-I	ABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (1 OF 17)							
Address	Bit Address	Data	Comments					
SFDP Header								
SFDP Heade	er: 1 st DWORD							
00H	A7:A0	53H	SFDP Signature					
01H	A15:A8	46H	SFDP Signature = 50444653H					
02H	A23:A16	44H						
03H	A31:A24	50H						
SFDP Heade	er: 2 nd DWORD							
04H	A7:A0	06H	SFDP Minor Revision Number					
05H	A15:A8	01H	SFDP Major Revision Number					
06H	A23:A16	02H	Number of Parameter Headers (NPH) = 3					
07H	A31:A24	FFH	Unused. Contains FF and can not be changed.					
			Parameter Headers					
JEDEC Flash Parameter Header: 1 st DWORD								
08H	A7:A0	00H	Parameter ID Least Significant Bit (LSB) Number. When this field is set to 00H, it indicates a JEDEC-specified header. For vendor-specified headers, this field must be set to the vendor's manufacturer ID.					
09H	A15:A8	06H	Parameter Table Minor Revision Number Minor revisions are either clarifications or changes that add parameters in existing Reserved locations. Minor revisions do NOT change overall structure of SFDP. Minor Revision starts at 00H.					
0AH	A23:A16	01H	Parameter Table Major Revision Number Major revisions are changes that reorganize or add parameters to locations that are NOT currently Reserved. Major revisions would require code (BIOS/firmware) or hardware change to get previously defined discoverable parameters. Major Revision starts at 01H.					
0BH	A31:A24	10H	Parameter Table Length Number of DWORDs that are in the Parameter table.					
JEDEC Flas	h Parameter H	eader: 2 nd DV	WORD					
0CH	A7:A0	30H	Parameter Table Pointer (PTP)					
0DH	A15:A8	00H	A 24-bit address that specifies the start of this header's Parameter table					
0EH	A23:A16	00H	in the SFDP structure. The address must be DWORD-aligned.					
0FH	A31:A24	FFH	Parameter ID Most Significant Bit (MSb) Number.					
			, ,					
JEDEC Sect	or Map Parame	eter Header:	3 rd DWORD					
10H	A7:A0	81H	Parameter ID LSB Number. Sector Map Function-Specific Table is assigned 81H.					
11H	A15:A8	00H	Parameter Table Minor Revision Number Minor revisions are either clarifications or changes that add parameters in existing Reserved locations. Minor revisions do NOT change overall structure of SFDP. Minor Revision starts at 00H.					
			Parameter Table Major Revision Number					
12H	A23:A16	01H	Major revisions are changes that reorganize or add parameters to locations that are NOT currently Reserved. Major revisions would require code (BIOS/firmware) or hardware change to get previously defined discoverable parameters. Major Revision starts at 01H.					
	1		suidance Detaile" for more detailed mapping information					

Note 1: See Section 11.1 "Mapping Guidance Details" for more detailed mapping information.

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (2 OF 17)

Address	Bit Address	Data	Comments
			Parameter Table Length
13H	A31:A24	06H	Number of DWORDs that are in the Parameter table.
JEDEC Flasi	n Parameter He	eader: 4 th DV	
14H	A7:A0	00H	Parameter Table Pointer (PTP)
15H	A15:A8	01H	This 24-bit address specifies the start of this header's Parameter Table in
16H	A23:A16	00H	the SFDP structure. The address must be DWORD-aligned.
17H	A31:A24	FFH	Parameter ID MSb
	endor) Parame		
wiicrociiip (v	endor) Parame	eter neauer.	ID Number
18H	A7:A0	BFH	
19H	A15:A8	00H	Manufacture ID (vendor specified header) Parameter Table Minor Revision Number
1AH	A23:A16	01H	Parameter Table major Revision Number, Revision 1.0
1BH	A31:A24	18H	Parameter Table Length, 24 Double Words
	endor) Parame		
1CH	A7:A0	00H	Parameter Table Pointer (PTP)
1DH	A15:A8	02H	This 24-bit address specifies the start of this header's Parameter Table in
1EH	A23:A16	00H	the SFDP structure. The address must be DWORD-aligned.
1FH	A31:A24	01H	Used to indicate bank number (vendor specific).
			JEDEC Flash Parameter Table
JEDEC Flasi	n Parameter Ta	ıble: 1 st DWC	ORD
			Block/Sector Erase Sizes
			00: Reserved
	A1:A0		01: 4-Kbyte Erase
			10: Reserved 11: Use this setting only if the 4-byte erase is unavailable.
			Write Granularity
	A2		0: Single-byte programmable devices or buffer programmable devices with buffer is less than 64 bytes (32 Words).
			1: For buffer programmable devices when the buffer size is 64 bytes
30H		FDH	(32 Words) or larger.
			Volatile STATUS Register
	А3		0: Target Flash has nonvolatile status bit. Write/Erase commands do not require STATUS register to be written on every power-on.
			1: Target Flash has volatile Status bits.
			Write Enable Opcode Select for Writing to Volatile STATUS Register
	A4		0: 0x50 Enables a STATUS register write when bit 3 is set to '1'.
			1: 0x06 Enables a STATUS register write when bit 3 is set to '1'.
	A7:A5		Unused. Contains 111b and can not be changed.
31H	A15:A8	20H	4-Kbyte Erase Opcode

Note 1: See Section 11.1 "Mapping Guidance Details" for more detailed mapping information.

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (3 OF 17)

Address	Bit Address	Data	Comments
			Supports (1-1-2) Fast Read
	A16		0: (1-1-2) Fast Read NOT supported
			1: (1-1-2) Fast Read supported
		Address Bytes Number of bytes used in addressing Flash array read, write and erase	
			00: 3-byte-only addressing
	A18:A17		01: 3- or 4-byte addressing (e.g. defaults to 3-byte mode; enters 4-byte mode on command)
			10: 4-byte-only addressing
			11: Reserved
			Supports Double Transfer Rate (DTR) Clocking
	A19		Indicates the device supports some type of double transfer rate clocking.
	Ala		0: DTR NOT supported
			1: DTR Clocking supported
32H	32H A20	F1H	Supports (1-2-2) Fast Read Device supports single input opcode, dual input address and dual output data Fast Read.
			0: (1-2-2) Fast Read NOT supported.
			1: (1-2-2) Fast Read supported.
	A21		Supports (1-4-4) Fast Read Device supports single input opcode, quad input address and quad output data Fast Read.
	7		0: (1-4-4) Fast Read NOT supported.
			1: (1-4-4) Fast Read supported.
			Supports (1-1-4) Fast Read
	A22		Device supports single input opcode & address and quad output data Fast Read.
			0: (1-1-4) Fast Read NOT supported.
			1: (1-1-4) Fast Read supported.
	A23		Unused. Contains '1' cannot be changed.
33H	A31:A24	FFH	Unused. Contains FF can not be changed
JEDEC Flash	n Parameter Ta	able: 2 nd DWC	DRD
34H	A7:A0	FFH	Flash Memory Density
35H	A15:A8	FFH	SST26VF016B = 00FFFFFFH
36H	A23:A16	FFH	
37H	A31:A24	00H	

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (4 OF 17)

Address	Bit Address	Data	Comments		
JEDEC Flasi	JEDEC Flash Parameter Table: 3 rd DWORD				
	A4:A0	- 44H	(1-4-4) Fast Read Number of Wait states (dummy clocks) needed before valid output		
38H			00100b: 4 dummy clocks (16 dummy bits) are needed with a quad input address phase instruction.		
0011	A7:A5		Quad Input Address Quad Output (1-4-4) Fast Read Number of Mode Bits		
			010b: 2 dummy clocks (8 mode bits) are needed with a single input opcode, quad input address and quad output data Fast Read instruction.		
39H	A15:A8	EBH	(1-4-4) Fast Read Opcode Opcode for single input opcode, quad input address and quad output data Fast Read.		
	A20:A16	08H	(1-1-4) Fast Read Number of Wait states (dummy clocks) needed before valid output		
ЗАН			01000b: 8 dummy bits are needed with a single input opcode & address and quad output data Fast Read instruction.		
			(1-1-4) Fast Read Number of Mode Bits		
	A23:A21		000b: No mode bits are needed with a single input opcode & address and quad output data Fast Read instruction.		
3ВН	A31:A24	6BH	(1-1-4) Fast Read Opcode Opcode for single input opcode & address and quad output data Fast Read.		
JEDEC Flasi	JEDEC Flash Parameter Table: 4 th DWORD				
	A4:A0	08H	(1-1-2) Fast Read Number of Wait states (dummy clocks) needed before valid output 01000b: 8 dummy clocks are needed with a single input opcode,		
3CH			address and dual output data fast read instruction.		
	A7:A5		(1-1-2) Fast Read Number of Mode Bits 000b: No mode bits are needed with a single input opcode & address and quad output data Fast Read instruction.		
3DH	A15:A8	3BH	(1-1-2) Fast Read Opcode Opcode for single input opcode & address and dual output data Fast Read.		
3EH	A20:A16	80H	(1-2-2) Fast Read Number of Wait states (dummy clocks) needed before valid output 00010b: 0 clocks of dummy cycle.		
	A23:A21		(1-2-2) Fast Read Number of Mode Bits (in clocks) 010b: 4 clocks of mode bits are needed.		
3FH	A31:A24	ввн	(1-2-2) Fast Read Opcode Opcode for single input opcode, dual input address and dual output data Fast Read.		

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (5 OF 17)

Address	Bit Address	Data	Comments	
JEDEC Flash Parameter Table: 5 th DWORD				
	A0	- FEH	Supports (2-2-2) Fast Read Device supports dual input opcode & address and dual output data Fast Read. 0: (2-2-2) Fast Read NOT supported. 1: (2-2-2) Fast Read supported.	
4011	A3:A1		Reserved. Bits default to all 1's.	
40H	A4		Supports (4-4-4) Fast Read Device supports Quad input opcode & address and quad output data Fast Read. 0: (4-4-4) Fast Read NOT supported. 1: (4-4-4) Fast Read supported.	
	A7:A5		Reserved. Bits default to all 1's.	
41H	A15:A8	FFH	Reserved. Bits default to all 1's.	
42H	A23:A16	FFH	Reserved. Bits default to all 1's.	
43H	A31:A24	FFH	Reserved. Bits default to all 1's.	
JEDEC Flash Parameter Table: 6 th DWORD				
44H	A7:A0	FFH	Reserved. Bits default to all 1's.	
45H	A15:A8	FFH	Reserved. Bits default to all 1's.	
46H	A20:A16	00H	(2-2-2) Fast Read Number of Wait states (dummy clocks) needed before valid output 00000b: No dummy bit is needed.	
	A23:A21		(2-2-2) Fast Read Number of Mode Bits 000b: No mode bits are needed.	
47H	A31:A24	FFH	(2-2-2) Fast Read Opcode Opcode for dual input opcode & address and dual output data Fast Read (not supported).	
JEDEC Flash	n Parameter Ta	able: 7 th DWC	DRD	
48H	A7:A0	FFH	Reserved. Bits default to all 1's.	
49H	A15:A8	FFH	Reserved. Bits default to all 1's.	
4AH	A20:A16	44H	(4-4-4) Fast Read Number of Wait states (dummy clocks) needed before valid output 00100b: 4 clocks dummy are needed with a quad input opcode & address and quad output data Fast Read instruction. (4-4-4) Fast Read Number of Mode Bits	
	A23:A21		010b: 2 clocks mode bits are needed with a quad input opcode & address and quad output data Fast Read instruction.	
4BH	A31:A24	0BH	(4-4-4) Fast Read Opcode Opcode for quad input opcode/address, quad output data Fast Read.	
JEDEC Flash Parameter Table: 8 th DWORD				
4CH	A7:A0	0CH	Sector Type 1 Size 4-Kbyte, Sector/block size = 2 ^N bytes	
4DH	A15:A8	20H	Sector Type 1 Opcode Opcode used to erase the number of bytes specified by Sector Type 1 Size.	
4EH	A23:A16	0DH	Sector Type 2 Size 8-Kbyte, Sector/block size = 2 ^N bytes	

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (6 OF 17)

Address	Bit Address	Data	Comments
4FH	A31:A24	D8H	Sector Type 2 Opcode Opcode used to erase the number of bytes specified by Sector Type 2 Size
JEDEC Flas	h Parameter Ta	ıble: 9 th DW0	ORD
50H	A7:A0	0FH	Sector Type 3 Size 32-Kbyte, Sector/block size = 2 ^N bytes
51H	A15:A8	D8H	Sector Type 3 Opcode Opcode used to erase the number of bytes specified by Sector Type 3 Size
52H	A23:A16	10H	Sector Type 4 Size 64-Kbyte, Sector/block size = 2 ^N bytes
53H	A31:A24	D8H	Sector Type 4 Opcode Opcode used to erase the number of bytes specified by Sector Type 4 Size
JEDEC Flas	h Parameter Ta	ıble: 10 th DW	/ORD
54H	A3:A0	20H	Multiplier from typical erase time to maximum erase time Maximum time = 2*(count + 1)*Typical erase time Count = 0 A3:A0 = 0000b
	A7:A4		Erase Type 1 Erase, Typical time Typical Time = (count +1)*units 1 ms to 32 ms, 16 ms to 512 ms, 128 ms to 4096 ms, 1s to 32s 10:9 units (00b: 1 ms, 01b: 16 ms, 10b:128 ms, 11b:1s) A8:A4 count = 18 = 10010b A10:A9 unit = 1 ms = 00b
	A10:A8		A10:A8 = 001b
55H	A15:A11	91H	Erase Type 2 Erase, Typical time Typical time = (count+1)*units 1 ms to 32 ms, 16 ms to 512 ms, 128 ms to 4096 ms, 1s to 32s 17:16 units (00b: 1 ms, 01b: 16 ms, 10b: 128 ms, 11b: 1s) A15:A11 count = 18 = 10010b A17:A16 unit = 1 ms = 00b
	A17:A16	48H	A17:A16 = 00b
56H	A23:A18		Erase Type 3 Erase, Typical time Typical time = (count+1)*units 1 ms to 32 ms, 16 ms to 512 ms, 128 ms to 4096 ms, 1s to 32s 24:23 units (00b: 1 ms, 01b: 16 ms, 10b: 128 ms, 11b: 1s) A22:A18 count = 18 = 10010b A24:A23 unit = 1 ms = 00b
	A24	24H	A24 = 0b
57H	A31:A25		Erase Type 4 Erase, Typical time Typical time = (count+1)*units 1 ms to 32 ms, 16 ms to 512 ms, 128 ms to 4096 ms, 1s to 32s 31:30 units (00b: 1 ms, 01b: 16 ms, 10b: 128 ms, 11b: 1s) A29:A25 count = 18 = 10010b A31:A30 unit = 1ms = 00b

Note 1: See Section 11.1 "Mapping Guidance Details" for more detailed mapping information.

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (7 OF 17)

Address	Bit Address	Data	Comments	
JEDEC Flash	JEDEC Flash Parameter Table: 11 th DWORD			
58H	A3:A0	- 80Н	Multiplier from Typical Program Time to Maximum Program Time Maximum time = 2*(count +1)*Typical program time Count = 0 A3:A0 = 0000b	
	A7:A4		Page Size Page size = 2 ^N bytes N = 8 A7:A4 = 1000b	
59H	A13:A8	- 6FH	Page Program Typical time Program time = (count+1)*units 13 units (0b: 8 μs, 1b: 64 μs) A12:A8 count = 11 = 01111b A13 unit = 64 μs = 1b	
	A15:A14		Byte Program Typical time, first byte Typical time = (count+1)*units 18 units (0b: 1 μs, 1b: 8 μs) A17:A14 count = 5 = 0101b A18 = 8 μs = 1b	
	A18:A16	1DH	A18:A16 = 101b	
5AH	A23:A19		Byte Program Typical time, Additional Byte Typical time = (count+1)*units 23 units (0b: 1 μs, 1b: 8 μs) A22:A19 count = 0011b A23 = 1 μs = 0b	
5BH	A30:A:24	81H	Chip Erase Typical Time Typical time = (count+1)*units 16 ms to 512 ms, 256 ms to 8192 ms, 4s to 128s, 64s to 2048s A28:A24 count = 1 = 00001b A30:A29 units = 16 ms = 00b	
	A31		Reserved A31 = 1b	

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (8 OF 17)

Address	Bit Address	Data	Comments
JEDEC Flash	n Parameter Ta	able: 12 th DW	ORD
5CH	A3:A0	- EDH	Prohibited Operations During Program Suspend xxx0b: May not initiate a new erase anywhere. xxx1b: May not initiate a new erase in the program suspended page size. xx0xb: May not initiate a new page program anywhere. xx1xb: May not initiate a new page program in program suspended page size. x0xxb: Refer to the Data Sheet. x1xxb: May not initiate a read in the program suspended page size. 0xxxb: Additional erase or program restrictions apply. 1xxxb: The erase and program restrictions in bits 1:0 are sufficient.
	A7:A4		Prohibited Operation During Erase Suspend xxx0b: May not initiate a new erase anywhere. xxx1b: May not initiate a new erase in the erase suspended page size. xx0xb: May not initiate a new page program anywhere. xx1xb: May not initiate a new page program in erase suspended erase type size. x0xxb: Refer to the Data Sheet. x1xxb: May not initiate a read in the erase suspended page size. 0xxxb: Additional erase or program restrictions apply. 1xxxb: The erase and program restrictions in bits 5:4 are sufficient.
	A8		Reserved = 1b
5DH	A12:A9	OFH	Program Resume to Suspend Interval The device requires this typical amount of time to make progress on the program operation before allowing another suspend. Interval = $500 \ \mu s$ Program resume to suspend interval = $(count+1)*64 \ \mu s$ A12:A9= 7 = 0111b
	A15:A13		Suspend In-progress Program Max Latency Maximum time required by the Flash device to suspend an in-progress program and be ready to accept another command which accesses the Flash array. Maximum latency = 25.μs program maximum latency =.(count+1)*units units (00b: 128 ns, 01b: 1 μs, 10b: 8 μs, 11b: 64 μs) A17:A13 = count = 24 = 11000b A19:A18 = 1μs = 01b
	A19:A16		0111b
5EH	A23:A20	77H	Erase Resume to Suspend Interval The device requires this typical amount of time to make progress on the erase operation before allowing another suspend. Interval = 500 μs Erase resume to suspend interval = (count+1)*64 μs A23:A20 = 7 = 0111b

Note 1: See Section 11.1 "Mapping Guidance Details" for more detailed mapping information.

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (9 OF 17)

Address	Bit Address	Data	Comments
5FH	A30:A24	38H	Suspend In-progress Erase Maximum Latency Maximum time required by the Flash device to suspend an in-progress erase and be ready to accept another command which accesses the Flash array. Maximum latency = 25 μs Erase maximum latency = .(count+1)*units units (00b: 128 ns, 01b: 1 μs, 10b: 8 μs, 11b: 64 μs) A28:A24 = count = 24 = 11000b A30:A29 = 1 μs = 01b
	A31		Suspend/Resume supported 0: supported 1: not supported
JEDEC Flash	Parameter Ta	able: 13 th DW	ORD
60H	A7:A0	30H	Program Resume Instruction
61H	A15:A8	ВОН	Program Suspend Instruction
62H	A23:A16	30H	Resume Instruction
63H	A31:A24	ВОН	Suspend Instruction
JEDEC Flash	Parameter Ta	able: 14 th DW	ORD
	A1:A0		Reserved = 11b
64H	A7:A2	F7H	STATUS Register Polling Device Busy 111101b: Use of legacy polling is supported by reading the STATUS register with 05h instruction and checking WIP bit [0] (0 = ready, 1 = busy).
65H	A14:A8	А9Н	Exit Deep Power-down to next operation delay: 10 μs Delay = (count+1)*unit A12:A8 = count = 9 = 01001b A14:A13 units = 01b = 1 μs
	A15		Exit Power-down Instruction: ABH = 10101011b A15 = 1b
	A22:A16	D5H	A22:A16 = 1010101b
66H	A23		Enter Power-down instruction: B9H = 10111001b A23 = 1b
	A30:A24		A30:A24 = 1011100
67H	A31	5CH	Deep Power-down Supported 0: supported 1: not supported
JEDEC Flash	Parameter Ta	able: 15 th DW	ORD
68H	A3:A0	29H	4-4-4 Mode Disable Sequences Xxx1b: issue FF instruction. 1xxxb: issue the Soft Reset 66/99 sequence.
	A7:A4		4-4-4 mode enable sequences X_xx1xb: issue instruction 38h.

Note 1: See Section 11.1 "Mapping Guidance Details" for more detailed mapping information.

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (10 OF 17)

Address	1		Comments	
Auuress	Bit Address	Data	Comments	
	A8		4-4-4 Mode Enable Sequences A8 = 0	
			0-4-4 Mode Supported	
69H	A9	C2H	0: not supported	
0311		OZIT	1: supported	
	A15.A10		0-4-4 Mode Exit Method	
	A15:A10		X1_xxxx: Mode Bit[7:0] Not = AXh 1x xxxx: Reserved = 1	
			0-4-4 Mode Entry Method	
İ	A19:A16		X1xxb: M[7:0] = AXh	
			1xxxb: Reserved = 1	
6AH	A22:A20	5CH	Quad Enable Requirements (QER) 101b: Quad Enable is bit 1 of the Configuration register.	
			HOLD and Reset Disable	
	A23		0: feature is not supported.	
6BH	A31:A24	FFH	Reserved bits = 0xFF	
JEDEC Flasi	h Parameter Ta	able: 16 th DW	ORD	
	1		Volatile or Nonvolatile Register and Write Enable Instructions for	
			STATUS Register 1	
	A6:A0		Xx1_xxxxb: STATUS Register 1 contains a mix of volatile and nonvola-	
6C		F0H	tile bits. The 06h instruction is used to enable writing to the register. X1x xxxxb: Reserved = 1	
			1xx_xxxxb: Reserved = 1	
	A7		Reserved = 1b	
			Soft Reset and Rescue Sequence Support	
	A13:A8		X1_xxxxb: Reset enable instruction 66h is issued followed by Reset instruction 99h.	
6D		30H	1x xxxxb: exit 0-4-4 mode is required prior to other Reset sequences.	
	0.45.044		Exit 4-byte Addressing	
	A15:A14		Not supported	
			Exit 4-byte Addressing	
6E	A23:A16	C0H	Not supported A21:A14 = 000000b	
			A23 and A22 are Reserved bits which are = 1	
			Enter 4-byte Addressing	
6F	A31:A24	80H	Not supported	
			1xxx_xxxx: Reserved = 1	
JEDEC Sect	or Map Paramo	eter Table		
			Sector Map	
100H	A7:A0	FFH	A7:A2 = Reserved = 1111111b A1 = Descriptor Type = Map = 1b	
			A0 = Last map = 1b	
101H	A15:A8	00H	Configuration ID = 00h	
102H	A23:A16	04H	Region Count = 5 Regions	
103H	A31:A24	FFH	Reserved = FFH	
			Region 0 supports 4-Kbyte erase and 8-Kbyte erase	
104H	A7:A0	F3H	A3:A0 = 0011b A7:A4 = Reserved = 1111b	
Note 1: Sc	1		widence Details" for more detailed manning information	

Note 1: See Section 11.1 "Mapping Guidance Details" for more detailed mapping information.

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (11 OF 17)

Address	Bit Address	Data	Comments	
105H	A15:A8	7FH	Region 0 Size 4 * 8 Kbytes = 32 Kbytes Count = 32 Kbytes/256 bytes = 128 Value = count -1 = 127 A31:A8 = 00007Fh	
106H	A23:A16	00H		
107H	A31:A24	00H		
108H	A7:A0	F5H	Region 1 supports 4-Kbyte erase and 32-Kbyte erase A3:A0 = 0101b A7:A4 = Reserved = 1111b	
109H	A15:A8	7FH	Region 1 size 1 * 32 Kbytes = 32Kbytes Count = 32 Kbytes/256 bytes = 128 Value = count -1 = 127 A31:A8 = 00007Fh	
10AH	A23:A16	00H		
10BH	A31:A24	00H		
10CH	A7:A0	F9H	Region 2 supports 4-Kbyte erase and 64-Kbyte erase A3:A0 = 1001b A7:A4 = Reserved = 1111b	
10DH	A15:A8	FFH	Region 2 size 30 * 64 Kbytes = 1920 Kbytes Count = 1920 Kbytes/256 bytes = 7680 Value = count -1 = 7679 A31:A8 = 001DFFh	
10EH	A23:A16	1DH		
10FH	A31:A24	00H		
110H	A7:A0	F5H	Region 3 supports 4-Kbyte erase and 32-Kbyte erase A3:A0 = 0101b A7:A4 = Reserved = 1111b	
111H	A15:A8	7FH	Region 3 size 1 * 32 Kbytes = 32 Kbytes Count = 32 Kbytes/256 bytes = 128 Value = count -1 = 127 A31:A8 = 00007Fh	
112H	A23:A16	00H		
113H	A31:A24	00H		
114H	A7:A0	F3H	Region 4 supports 4-Kbyte erase and 8-Kbyte erase A3:A0 = 0011b A7:A4 = Reserved = 1111b	
115H	A15:A8	7FH	Region 4 Size 4 * 8 Kbytes = 32 Kbytes Count = 32 Kbytes/256 bytes = 128 Value = count -1 = 127 A31:A8 = 00007Fh	
116H	A23:A16	00H		
117H	A31:A24	00H		

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (12 OF 17)

Address	Bit Address	Data	Comments			
	SST26VF016B (Vendor) Parameter Table					
SST26VF016	SST26VF016B Identification					
200H	A7:A0	BFH	Manufacturer ID			
201H	A15:A8	26H	Memory Type			
202H	A23:A16	41H	Device ID SST26VF016B = 41H			
203H	A31:A24	FFH	Reserved. Bits default to all 1's.			
SST26VF016	6B Interface					
	A2:A0		Interfaces Supported 000: SPI only 001: Power up default is SPI; Quad can be enabled/disabled 010: Reserved : : 111: Reserved			
204H	А3	В9Н	Supports Enable Quad 0: not supported 1: supported			
	A6:A4		Supports Hold#/Reset# Function 000: Hold# 001: Reset# 010: HOLD/Reset# 011: Hold# & I/O when in SQI(4-4-4), 1-4-4 or 1-1-4 Read			
	A7		Supports Software Reset 0: not supported 1: supported			
	A8		Supports Quad Reset 0: not supported 1: supported			
	A10:A9		Reserved. Bits default to all 1's.			
205H	A13:A11	DFH	Byte Program or Page Program (256 bytes) 011: Byte Program/Page Program in SPI and Quad Page Program once Quad is enabled			
	A14	1	Program Erase Suspend Supported 0: Not Supported 1: Program/Erase Suspend Supported			
	A15		Deep Power-Down Mode Supported 0: Not Supported 1: Deep Power-Down Mode Supported			

Note 1: See Section 11.1 "Mapping Guidance Details" for more detailed mapping information.

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (13 OF 17)

Address	Bit Address	Data	Comments	
	A16		OTP Capable (Security ID) Supported 0: not supported 1: supported	
	A17		Supports Block Group-Protect 0: not supported 1: supported	
206H	A18	FDH	Supports Independent Block-Protect 0: not supported 1: supported	
	A19		Supports Independent Nonvolatile Lock (Block or Sector becomes OTP) 0: not supported 1: supported	
	A23:A20		Reserved. Bits default to all 1's.	
207H	A31:A24	FFH	Reserved. Bits default to all 1's.	
208H	A7:A0	30H	VDD Minimum Supply Voltage	
209H	A15:A8	F2H	2.3V (F230H)	
20AH	A23:A16	60H	VDD Maximum Supply Voltage	
20BH	A31:A24	F3H	3.6V (F360H)	
20CH	A7:A0	32H	Typical time-out for Byte Program: 50 μs Typical time-out for Byte Program is in μs. Represented by conversion of the actual time from the decimal to hexadecimal number.	
20DH	A15:A8	FFH	H Reserved. Bits default to all 1's.	
20EH	A23:A16	0AH	Typical time-out for page program: 1.0 ms (xxH*(0.1 ms)	
20FH	A31:A24	12H	Typical time-out for Sector Erase/Block Erase: 18 ms Typical time-out for Sector/Block Erase is in ms. Represented by conversion of the actual time from the decimal to hexadecimal number.	
210H	A7:A0	23H	Typical time-out for Chip Erase: 35 ms Typical time out for Chip Erase is in ms. Represented by conversion of the actual time from the decimal to hexadecimal number.	
211H	A15:A8	46H	Maximum time-out for Byte Program: 70 μs Typical time-out for Byte Program is in μs. Represented by conversion of the actual time from the decimal to hexadecimal number.	
212H	A23:A16	FFH	Reserved. Bits default to all 1's.	
213H	A31:A24	0FH	Maximum time-out for Page Program: 1.5 ms. Typical time-out for Page Program in xxH * (0.1 ms) ms	
214H	A7:A0	19H	Maximum time-out for Sector Erase/Block Erase: 25 ms Maximum time-out for Sector/Block Erase in ms.	
215H	A15:A8	32H	Maximum time-out for Chip Erase: 50 ms Maximum time-out for Chip Erase in ms.	
216H	A23:A16	0FH	Maximum time out for Program Security ID: 1.5 ms Maximum time-out for Program Security ID in xxH*(0.1 ms) ms	
217H	A31:A24	19H	Maximum time-out for Write Protection Enable Latency: 25 ms Maximum time-out for Write Protection Enable Latency is in ms. Represented by conversion of the actual time from the decimal to hexadecimal number.	
218H	A23:A16	19H	Maximum time Write Suspend Latency: 25 μs Maximum time out for Write Suspend Latency is in μs. Represented by conversion of the actual time from the decimal to hexadecimal number.	

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (14 OF 17)

Address	Bit Address	Data	Comments	
219H	A31:A24	03H	Maximum time to Deep Power-Down: 3 μs = 03H	
21AH	A23:A16	0AH	Maximum time-out from Deep Power-Down mode to Standby mode: 10 µs = 0AH	
21BH	A31:A24	FFH	Reserved. Bits default to all 1's.	
21CH	A23:A16	FFH	Reserved. Bits default to all 1's.	
21DH	A31:A24	FFH	Reserved. Bits default to all 1's.	
21EH	A23:A16	FFH	Reserved. Bits default to all 1's.	
21FH	A31:A24	FFH	Reserved. Bits default to all 1's.	
Supported In	nstructions			
220H	A7:A0	00H	No Operation	
221H	A15:A8	66H	Reset Enable	
222H	A23:A16	99H	Reset Memory	
223H	A31:A24	38H	Enable Quad I/O	
224H	A7:A0	FFH	Reset Quad I/O	
225H	A15:A8	05H	Read STATUS Register	
226H	A23:A16	01H	Write STATUS Register	
227H	A31:A24	35H	Read Configuration Register	
228H	A7:A0	06H	Write Enable	
229H	A15:A8	04H	Write Disable	
22AH	A23:A16	02H	Byte Program or Page Program	
22BH	A31:A24	32H	SPI Quad Page Program	
22CH	A7:A0	ВОН	Suspends Program/Erase	
22DH	A15:A8	30H	Resumes Program/Erase	
22EH	A23:A16	72H	Read Block Protection register	
22FH	A31:A24	42H	Write Block Protection Register	
230H	A7:A0	8DH	Lock Down Block Protection Register	
231H	A15:A8	E8H	Nonvolatile Write-Lock Down Register	
232H	A23:A16	98H	Global Block Protection Unlock	
233H	A31:A24	88H	Read Security ID	
234H	A7:A0	A5H	Program User Security ID Area	
235H	A15:A8	85H	Lockout Security ID Programming	
236H	A23:A16	C0H	Set Burst Length	
237H	A31:A24	9FH	JEDEC-ID	
238H	A7:A0	AFH	Quad J-ID	
239H	A15:A8	5AH	SFDP	
23AH	A23:A16	В9Н	Deep Power-Down Mode	
23BH	A31:A24	ABH	Release Deep Power-Down Mode	
23CH	A4:A0	06H	(1-4-4) SPI nB Burst with Wrap Number of Wait states (dummy clocks) needed before valid output 00110b: 6 clocks of dummy cycle	
	A7:A5		(1-4-4) SPI nB Burst with Wrap Number of Mode Bits	
23DH	A15:A8	ECH	(1-4-4) SPI nB Burst with Wrap Opcode	

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (15 OF 17)

Address	Bit Address	Data	Com	ments
23EH	A20:A16	06H	(4-4-4) SQI nB Burst with Wrap Nu clocks) needed before valid outpu 00110b: 6 clocks of dummy cycle	` ` `
	A23:A21		(4-4-4) SQI nB Burst with Wrap No	
23FH	A31:A24	0CH	(4-4-4) SQI nB Burst with Wrap Op	ocode
240H	A4:A0	00H	(1-1-1) Read Memory Number of Wait states (dummy clocks) needed before valid output 00000b: Wait states/dummy clocks are not supported.	
	A7:A5		(1-1-1) Read Memory Number of Noob: Mode bits are not supported.	node bits
241H	A15:A8	03H	(1-1-1) Read Memory Opcode	
242H	A20:A16	08H	(1-1-1) Read Memory at Higher Sp (dummy clocks) needed before va 01000: 8 clocks (8 bits) of dummy c	alid output cycle
	A23:A21		(1-1-1) Read Memory at Higher Sp	peed Number of Mode Bits
243H	A31:A24	0BH	(1-1-1) Read Memory at Higher Sp	peed Opcode
244H	A7:A0	FFH	Reserved. Bits default to all 1's.	
245H	A15:A8	FFH	Reserved. Bits default to all 1's.	
246H	A23:A16	FFH	Reserved. Bits default to all 1's.	
247H	A31:A24	FFH	Reserved. Bits default to all 1's.	
Security ID				
248H	A7:A0	FFH	Security ID size in bytes	
249H	A15:A8	07H	Example: If the size is 2 Kbytes, this Security I Unique ID (pre-programmed at factory) User-programmable	
24AH	A23:A16	FFH	Reserved. Bits default to all 1's.	
24BH	A31:A24	FFH	Reserved. Bits default to all 1's.	
Memory Org	anization/Bloc	k Protection	Bit Mapping ⁽¹⁾	
24CH	A7:A0	02H	Section 1: Sector Type Number: Sector type in JEDEC Parameter Table (bottom, 8-Kbyte)	
24DH	A15:A8	02H	Section 1 Number of Sectors Four of 8KB block (2 ⁿ)	
24EH	A23:A16	FFH	Section 1 Block Protection Bit Start ((2 ^m) +1)+ c, c = FFH or -1, m = 5 for 16 Mb Address bits are Read Lock bit locations and Even Address bits are Write Lock bit locations. The Most Significant (left-most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one then the number is less than zero or negative.	

Note 1: See Section 11.1 "Mapping Guidance Details" for more detailed mapping information.

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (16 OF 17)

Address	Bit Address	Data	Comments
24FH	A31:A24	06H	Section 1 (bottom) Block Protection Bit End ((2 ^m) +1)+ c, c = 06H or 6, m = 5 for 16 Mb Address bits are Read Lock bit locations and Even Address bits are Write Lock bit locations. The Most Significant (left-most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one then the number is less than zero or negative.
250H	A7:A0	03H	Section 2: Sector Type Number Sector type in JEDEC Parameter Table (32 KB Block)
251H	A15:A8	00H	Section 2 Number of Sectors One of 32 KB Block (2 ⁿ , n=0)
252H	A23:A16	FDH	Section 2 Block Protection Bit Start ((2 ^m) +1)+ c, c = FDH or -3, m = 5 for 16 Mb The Most Significant (left-most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one then the number is less than zero or negative.
253H	A31:A24	FDH	Section 2 Block Protection Bit End ((2 ^m) +1)+ c, c = FDH or -3, m = 5 for 16 Mb The Most Significant (left-most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one then the number is less than zero or negative.
254H	A7:A0	04H	Section 3: Sector Type Number Sector type in JEDEC Parameter Table (64 KB Block)
255H	A15:A8	05H	Section 3 Number of Sectors 126 of 64 KB Block (2 ⁿ - 2, n = 5 for 16 Mb
256H	A23:A16	00H	Section 3 Block Protection Bit Start Section 3 Block Protection Bit starts at 00H
257H	A31:A24	FCH	Section 3 Block Protection Bit End ((2 ^m) +1) + c, c = FCH or -4, m = 5 for 16 Mb
258H	A7:A0	03H	Section 4: Sector Type Number Sector type in JEDEC Parameter Table (32 KB Block)
259H	A15:A8	00H	Section 4 Number of Sectors One of 32 KB Block (2 ⁿ , n = 0)
25AH	A23:A16	FEH	Section 4 Block Protection Bit Start ((2 ^m) +1) + c, c = FEH or -2, m = 5 for 16 Mb The Most Significant (left-most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one then the number is less than zero or negative.
25BH	A31:A24	FEH	Section 4 Block Protection Bit End ((2 ^m) +1) + c, c = FEH or -2, m = 5 for 16 Mb The Most Significant (left-most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one then the number is less than zero or negative.
25CH	A7:A0	02H	Section 5 Sector Type Number: Sector type in JEDEC Parameter Table (top, 8-Kbyte)
25DH	A15:A8	02H	Section 5 Number of Sectors Four of 8 KB block (2^n)

TABLE 11-1: SERIAL FLASH DISCOVERABLE PARAMETER (SFDP) (CONTINUED) (17 OF 17)

Address	Bit Address	Data	Comments	
25EH	A23:A16	07H	Section 5 Block Protection Bit Start $((2^m) + 1) + c$, $c = 07H$ or 7, $m = 5$ for 16 Mb Address bits are Read Lock bit locations and Even Address bits are Write Lock bit locations. The Most Significant (left-most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one then the number is less than zero or negative.	
25FH	A31:A24	0EH	Section 5 (bottom) Block Protection Bit End (((2 ^m) +1) + c, c = 0EH or 14, m = 5 for 16 Mb Address bits are Read Lock bit locations and Even Address bits are Write Lock bit locations. The Most Significant (left-most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one then the number is less than zero or negative.	

Note 1: See Section 11.1 "Mapping Guidance Details" for more detailed mapping information.

11.1 Mapping Guidance Details

The SFDP Memory Organization/Block Protection Bit Mapping defines the memory organization including uniform sector/block sizes and different contiguous sectors/blocks sizes. In addition, this bit defines the number of these uniform and different sectors/blocks from address 000000H to the full range of Memory and the associated Block Locking Register bits of each sector/block.

Each major Section is defined as follows:

TABLE 11-2: SECTION DEFINITION

	Section X: Sector Type Number
Major Section X	Section X: Number of Sectors
Major Section X	Section X: Block-Protection Register Bit Start Location
	Section X: Block-Protection Register Bit End Location

A Major Section consists of Sector Type Number, Number of Sector of this type and the Block Protection Bit Start/End locations. This is tied directly to JEDEC Flash Parameter Table Sector Size Type (in 7th DWORD and 8th DWORD section). Note that the contiguous 4-Kbyte Sectors across the full memory range are not included on this section because they are not defined in the JEDEC Flash Parameter Table Sector Size Type section. Only the sectors/blocks that are dependently tied with the Block Protection Register bits are defined. A major section is a partition of contiguous same-size sectors/blocks. There will be several Major Sections as you dissect across memory from 000000h to the full range. Similar sector/block size that re-appear may be defined as a different Major Section.

11.1.1 SECTOR TYPE NUMBER

Sector Type Number is the sector/block size typed defined in JEDEC Flash Parameter Table: SFDP address locations 4CH, 4EH, 50H and 52H. Sector Type 1, which is represented by 01H, is located at address 4CH. Sector Type 2, which is represented by 02H, is located at address location 4EH. Sector Type 3, which is represented by 03H, is located at address location 50H. Sector Type 4, represented by 04H, is located at address location 52H. Contiguous Same Sector Type # Size can re-emerge across the memory range and this Sector Type # will indicate that it is a separate/independent Major Section from the previous contiguous sectors/blocks.

11.1.2 NUMBER OF SECTORS

Number of Sectors represents the number of contiguous sectors/blocks with similar size. A formula calculates the contiguous sectors/blocks with similar size. Given the sector/block size, type and the number of sectors, the address range of these sectors/blocks can be determined along with specific Block Locking Register bits that control the read/write protection of each sector/block.

11.1.3 BLOCK PROTECTION REGISTER BIT START LOCATION (BPSL)

Block Protection Register Bit Start Location (BPSL) designates the start bit location in the Block Protection Register where the first sector/block of this Major Section begins. If the value of BPSL is 00H, this location is the 0 bit location. If the value is other than 0, then this value is a constant value adder (c) for a given formula, $(2^m + 1) + (c)$ (see Section 11.1.5 "Memory Configuration").

From the initial location, there will be a bit location for every increment by 1 until it reaches the Block Protection Register Bit End Location (BPEL). This number range from BPSL to BPEL will correspond to and be equal to the number of sectors/blocks on this Major Section.

11.1.4 BLOCK PROTECTION REGISTER BIT END LOCATION (BPEL)

Block Protection Register Bit End Location designates the end bit location in the Block Protection Register bit where the last sector/block of this Major Section ends. The value in this field is a constant value adder (c) for a given formula or equation, $(2^m + 1) + (c)$ (see Section 11.1.5 "Memory Configuration").

11.1.5 MEMORY CONFIGURATION

For the SST26VF016B family, the memory configuration is setup with different contiguous block sizes from bottom to the top of the memory. For example, starting from bottom of memory it has four 8-Kbyte blocks, one 32-Kbyte block, x number of 64-Kbyte blocks depending on memory size, then one 32-Kbyte block and four 8-Kbyte block on the top of memory (see Table 11-3).

TABLE 11-3: MEMORY BLOCK DIAGRAM REPRESENTATION

	Section 1: Sector Type Number
8-Kbyte Bottom Block	Section 1: Number of Sectors
(from 000000H)	Section 1: Block Protection Register Bit Start Location
	Section 1: Block Protection Register Bit End Location
	Section 2: Sector Type Number
22 Khuta	Section 2: Number of Sectors
32-Kbyte	Section 2: Block Protection Register Bit Start Location
	Section 2: Bloc Protection Register Bit End Location
	Section 3: Sector Type Number
64 Khyto	Section 3: Number of Sectors
64-Kbyte	Section 3: Block Protection Register Bit Start Location
	Section 3: Block Protection Register Bit End Location
	Section 4: Sector Type Number
32 Khyto	Section 4: Number of Sectors
32-Kbyte	Section 4: Block Protection Register Bit Start Location
	Section 4: Block Protection Register Bit End Location
	Section 5: Sector Type Number
9 Khyta (Tan Black)	Section 5: Number of Sectors
8-Kbyte (Top Block)	Section 5: Block Protection Register Bit Start Location
	Section 5: Block Protection Register Bit End Location

Classifying these sector/block sizes via the Sector Type derived from JEDEC Flash Parameter Table: SFDP address locations 4EH, 50H and 52H are as follows:

- 8-Kbyte Blocks are classified as Sector Type 2 (@4EH of SFDP)
- 32-Kbyte Blocks are classified as Sector Type 3 (@50H of SFDP)
- 64-Kbyte Blocks are classified as Sector Type 4 (@52H of SFDP)

For the Number of Sectors associated with the contiguous sectors/blocks, a formula is used to determine the number of sectors/blocks of these Sector Types:

- 8-Kbyte Block (Type 2) is calculated by 2ⁿ. n is a byte.
- 32-Kbyte Block (Type 3) is calculated by 2ⁿ. n is a byte.
- 64-Kbyte Block (Type 4) is calculated by (2m 2).
 m can either be a 4, 5, 6, 7 or 8 depending on the
 memory size. This m field is going to be used for
 the 64-Kbyte Block Section and will also be used
 for the Block Protection Register Bit Location formula.

m will have a constant value for specific densities and is defined as:

- 8 Mbit = 4
- 16 Mbit = 5
- 32 Mbit = 6
- 64 Mbit = 7
- 128 Mbit = 8

Block-Protect Register Start/End Bits are mapped in the SFDP by using the formula $(2^m + 1) + (c)$. "m" is a constant value that represents the different densities from 8 Mbit to 128 Mbit (used also in the formula calculating number of 64-Kbyte Blocks above). The values that are going to be placed in the Block Protection Bit Start/End field table are the constant value adder (c) in the formula and are represented in two's compliment except when the value is 00H. If the value is 00H, this location is the 0 bit location. If the value is other than 0. then this is a constant value adder (c) that will be used in the formula. The Most Significant (left most) bit indicates the sign of the integer; it is sometimes called the sign bit. If the sign bit is zero, then the number is greater than or equal to zero, or positive. If the sign bit is one, then the number is less than zero, or negative. See Table 11-4 for an example of this formula.

TABLE 11-4: BPSL/BPEL EQUATION WITH ACTUAL CONSTANT ADDER DERIVED FROM THE FORMULA $(2^M + 1) + (C)$

Block Size	8 Mbit to 128 Mbit	Comments
8-Kbyte (Type 2) Bottom	BPSL = (2 ^m + 1) + 0FFH BPEL = (2 ^m + 1) + 04H	OFFH = -1; 06H = 6 Odd address bits are Read Lock bit locations and even address bits are Write Lock bit locations.
32-Kbyte (Type3)	BPSL = BPEL= (2 ^m + 1) + 0FDH	0FDH = -3
64-Kbyte (Type 4)	BPSL = 00H BPEL = (2 ^m + 1) + 0FCH	00H is Block Protection Register bit 0 location; 0FCH = -4
32-Kbyte (Type 3)	BPSL = BPEL= (2 ^m + 1) + 0FEH	0FEH = -2
8-Kbyte (Type 2) Top	BPSL = (2 ^m + 1) + 07H BPEL = (2 ^m + 1) + 0EH	07H = 7; 0EH = 14 Odd address bits are Read Lock bit locations and even address bits are Write Lock bit locations.

Note the following details of the code protection feature on Microchip products:

- Microchip products meet the specifications contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is secure when used in the intended manner, within operating specifications, and under normal conditions.
- Microchip values and aggressively protects its intellectual property rights. Attempts to breach the code protection features of Microchip product is strictly prohibited and may violate the Digital Millennium Copyright Act.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of its code. Code protection does not
 mean that we are guaranteeing the product is "unbreakable". Code protection is constantly evolving. Microchip is committed to
 continuously improving the code protection features of our products.

This publication and the information herein may be used only with Microchip products, including to design, test, and integrate Microchip products with your application. Use of this information in any other manner violates these terms. Information regarding device applications is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. Contact your local Microchip sales office for additional support or, obtain additional support at https://www.microchip.com/en-us/support/design-help/client-support-services.

THIS INFORMATION IS PROVIDED BY MICROCHIP "AS IS". MICROCHIP MAKES NO REPRESENTATIONS OR WARRANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION INCLUDING BUT NOT LIMITED TO ANY IMPLIED WARRANTIES OF NON-INFRINGEMENT, MERCHANTABILITY, AND FITNESS FOR A PARTICULAR PURPOSE, OR WARRANTIES RELATED TO ITS CONDITION, QUALITY, OR PERFORMANCE.

IN NO EVENT WILL MICROCHIP BE LIABLE FOR ANY INDIRECT, SPECIAL, PUNITIVE, INCIDENTAL, OR CONSEQUENTIAL LOSS, DAMAGE, COST, OR EXPENSE OF ANY KIND WHATSOEVER RELATED TO THE INFORMATION OR ITS USE, HOWEVER CAUSED, EVEN IF MICROCHIP HAS BEEN ADVISED OF THE POSSIBILITY OR THE DAMAGES ARE FORESEEABLE. TO THE FULLEST EXTENT ALLOWED BY LAW, MICROCHIP'S TOTAL LIABILITY ON ALL CLAIMS IN ANY WAY RELATED TO THE INFORMATION OR ITS USE WILL NOT EXCEED THE AMOUNT OF FEES, IF ANY, THAT YOU HAVE PAID DIRECTLY TO MICROCHIP FOR THE INFORMATION.

Use of Microchip devices in life support and/or safety applications is entirely at the buyer's risk, and the buyer agrees to defend, indemnify and hold harmless Microchip from any and all damages, claims, suits, or expenses resulting from such use. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights unless otherwise stated.

AMBA, Arm, Arm7, Arm7TDMI, Arm9, Arm11, Artisan, big.LITTLE, Cordio, CoreLink, CoreSight, Cortex, DesignStart, DynamIQ, Jazelle, Keil, Mali, Mbed, Mbed Enabled, NEON, POP, RealView, SecurCore, Socrates, Thumb, TrustZone, ULINK, ULINK2, ULINK-ME, ULINK-PLUS, ULINKpro, μVision, Versatile are trademarks or registered trademarks of Arm Limited (or its subsidiaries) in the US and/or elsewhere.

For information regarding Microchip's Quality Management Systems, please visit www.microchip.com/quality.

Trademarks

The Microchip name and logo, the Microchip logo, Adaptec, AnyRate, AVR, AVR logo, AVR Freaks, BesTime, BitCloud, CryptoMemory, CryptoRF, dsPIC, flexPWR, HELDO, IGLOO, JukeBlox, KeeLoq, Kleer, LANCheck, LinkMD, maXStylus, maXTouch, MediaLB, megaAVR, Microsemi, Microsemi logo, MOST, MOST logo, MPLAB, OptoLyzer, PIC, picoPower, PICSTART, PIC32 logo, PolarFire, Prochip Designer, QTouch, SAM-BA, SenGenuity, SpyNIC, SST, SST Logo, SuperFlash, Symmetricom, SyncServer, Tachyon, TimeSource, tinyAVR, UNI/O, Vectron, and XMEGA are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

AgileSwitch, APT, ClockWorks, The Embedded Control Solutions Company, EtherSynch, Flashtec, Hyper Speed Control, HyperLight Load, IntelliMOS, Libero, motorBench, mTouch, Powermite 3, Precision Edge, ProASIC, ProASIC Plus, ProASIC Plus logo, Quiet-Wire, SmartFusion, SyncWorld, Temux, TimeCesium, TimeHub, TimePictra, TimeProvider, TrueTime, WinPath, and ZL are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Adjacent Key Suppression, AKS, Analog-for-the-Digital Age, Any Capacitor, AnyIn, AnyOut, Augmented Switching, BlueSky, BodyCom, CodeGuard, CryptoAuthentication, CryptoAutomotive, CryptoCompanion, CryptoController, dsPICDEM, dsPICDEM.net, Dynamic Average Matching, DAM, ECAN, Espresso T1S, EtherGREEN, GridTime, IdealBridge, In-Circuit Serial Programming, ICSP, INICnet, Intelligent Paralleling, Inter-Chip Connectivity, JitterBlocker, Knob-on-Display, maxCrypto, maxView, memBrain, Mindi, MiWi, MPASM, MPF, MPLAB Certified logo, MPLIB, MPLINK, MultiTRAK, NetDetach, NVM Express, NVMe, Omniscient Code Generation, PICDEM, PICDEM.net, PICkit, PICtail, PowerSmart, PureSilicon, QMatrix, REAL ICE, Ripple Blocker, RTAX, RTG4, SAM-ICE, Serial Quad I/O, simpleMAP, SimpliPHY, SmartBuffer, SmartHLS, SMART-I.S., storClad, SQI, SuperSwitcher, SuperSwitcher II, Switchtec, SynchroPHY, Total Endurance, TSHARC, USBCheck, VariSense, VectorBlox, VeriPHY, ViewSpan, WiperLock, XpressConnect, and ZENA are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

 $\ensuremath{\mathsf{SQTP}}$ is a service mark of Microchip Technology Incorporated in the U.S.A.

The Adaptec logo, Frequency on Demand, Silicon Storage Technology, Symmcom, and Trusted Time are registered trademarks of Microchip Technology Inc. in other countries.

GestIC is a registered trademark of Microchip Technology Germany II GmbH & Co. KG, a subsidiary of Microchip Technology Inc., in other countries.

All other trademarks mentioned herein are property of their respective companies.

© 2014-2022, Microchip Technology Incorporated and its subsidiaries.

All Rights Reserved.

ISBN: 978-1-5224-9425-6



Worldwide Sales and Service

AMERICAS

Corporate Office 2355 West Chandler Blvd. Chandler, AZ 85224-6199

Tel: 480-792-7200 Fax: 480-792-7277 Technical Support:

http://www.microchip.com/ support

Web Address:

www.microchip.com

Atlanta Duluth, GA

Tel: 678-957-9614 Fax: 678-957-1455

Austin, TX Tel: 512-257-3370

Boston

Westborough, MA Tel: 774-760-0087 Fax: 774-760-0088

Chicago Itasca, IL

Tel: 630-285-0071 Fax: 630-285-0075

Dallas

Addison, TX Tel: 972-818-7423 Fax: 972-818-2924

Detroit Novi, MI

Tel: 248-848-4000

Houston, TX Tel: 281-894-5983

Tel: 281-894-598 Indianapolis

Noblesville, IN Tel: 317-773-8323 Fax: 317-773-5453 Tel: 317-536-2380

Los Angeles

Mission Viejo, CA Tel: 949-462-9523 Fax: 949-462-9608 Tel: 951-273-7800

Raleigh, NC Tel: 919-844-7510

New York, NY Tel: 631-435-6000

San Jose, CA Tel: 408-735-9110 Tel: 408-436-4270

Canada - Toronto Tel: 905-695-1980 Fax: 905-695-2078

ASIA/PACIFIC

Australia - Sydney Tel: 61-2-9868-6733

China - Beijing Tel: 86-10-8569-7000

China - Chengdu Tel: 86-28-8665-5511

China - Chongqing Tel: 86-23-8980-9588

China - Dongguan Tel: 86-769-8702-9880

China - Guangzhou Tel: 86-20-8755-8029

China - Hangzhou Tel: 86-571-8792-8115

China - Hong Kong SAR Tel: 852-2943-5100

China - Nanjing Tel: 86-25-8473-2460

China - Qingdao Tel: 86-532-8502-7355

China - Shanghai Tel: 86-21-3326-8000

China - Shenyang Tel: 86-24-2334-2829

China - Shenzhen Tel: 86-755-8864-2200

China - Suzhou Tel: 86-186-6233-1526

China - Wuhan Tel: 86-27-5980-5300

China - Xian Tel: 86-29-8833-7252

China - Xiamen Tel: 86-592-2388138

China - Zhuhai Tel: 86-756-3210040

ASIA/PACIFIC

India - Bangalore Tel: 91-80-3090-4444

India - New Delhi Tel: 91-11-4160-8631

India - Pune Tel: 91-20-4121-0141

Japan - Osaka Tel: 81-6-6152-7160

Japan - Tokyo Tel: 81-3-6880- 3770

Korea - Daegu

Tel: 82-53-744-4301 Korea - Seoul

Tel: 82-2-554-7200 Malaysia - Kuala Lumpur

Tel: 60-3-7651-7906

Malaysia - Penang Tel: 60-4-227-8870

Philippines - Manila Tel: 63-2-634-9065

Singapore Tel: 65-6334-8870

Taiwan - Hsin Chu Tel: 886-3-577-8366

Taiwan - Kaohsiung Tel: 886-7-213-7830

Taiwan - Taipei Tel: 886-2-2508-8600

Thailand - Bangkok Tel: 66-2-694-1351

Vietnam - Ho Chi Minh Tel: 84-28-5448-2100

EUROPE

Austria - Wels Tel: 43-7242-2244-39

Fax: 43-7242-2244-393 **Denmark - Copenhagen**

Tel: 45-4485-5910 Fax: 45-4485-2829

Finland - Espoo Tel: 358-9-4520-820

France - Paris
Tel: 33-1-69-53-63-20
Fax: 33-1-69-30-90-79

Germany - Garching Tel: 49-8931-9700

Germany - Haan Tel: 49-2129-3766400

Germany - Heilbronn Tel: 49-7131-72400

Germany - Karlsruhe Tel: 49-721-625370

Germany - Munich Tel: 49-89-627-144-0 Fax: 49-89-627-144-44

Germany - Rosenheim Tel: 49-8031-354-560

Israel - Ra'anana Tel: 972-9-744-7705

Italy - Milan Tel: 39-0331-742611 Fax: 39-0331-466781

Italy - Padova Tel: 39-049-7625286

Netherlands - Drunen Tel: 31-416-690399 Fax: 31-416-690340

Norway - Trondheim Tel: 47-7288-4388

Poland - Warsaw Tel: 48-22-3325737

Romania - Bucharest Tel: 40-21-407-87-50

Spain - Madrid Tel: 34-91-708-08-90 Fax: 34-91-708-08-91

Sweden - Gothenberg Tel: 46-31-704-60-40

Sweden - Stockholm Tel: 46-8-5090-4654

UK - Wokingham Tel: 44-118-921-5800 Fax: 44-118-921-5820